

Development of RF Front-End Chip for Wireless Communications

Department of Electrical and Electronic Engineering
Graduate School of Information Science and Electrical Engineering
Kyushu University

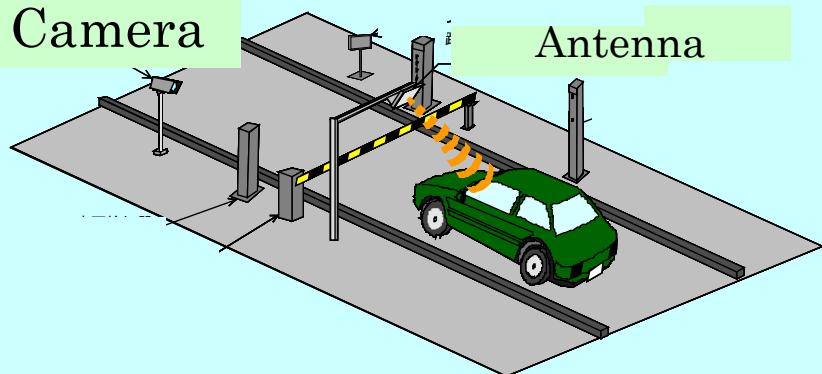
H. Kanaya, R. K. Pokharel and K. Yoshida

<http://yossvr0.ed.kyushu-u.ac.jp>

Driving Force: Wireless Technologies

Wireless LAN, Cell Phone, Cordless Telephone, IC Card, ITS, DSRC

Camera

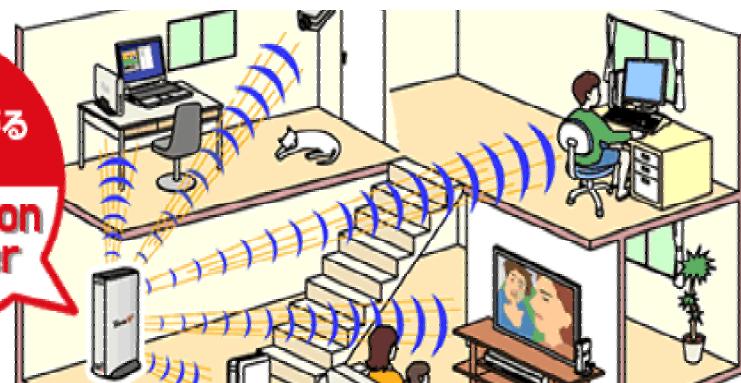


Antenna

Electronic-Toll Collection System.

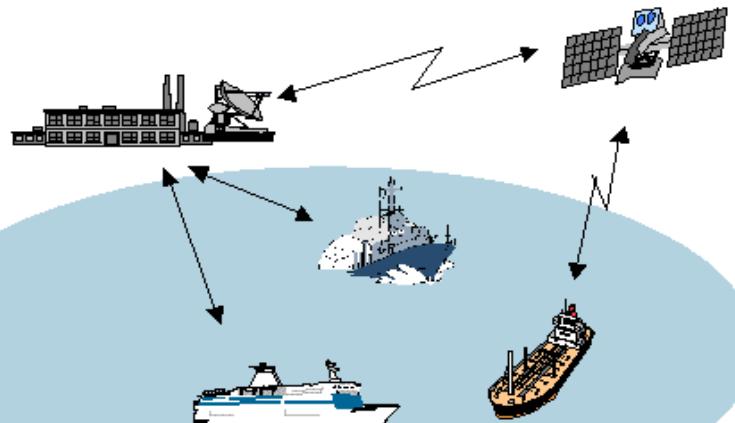
家中つながる

AirStation
Booster



Wireless LAN

Satellite Communications



Cell Phone Cordless Phone

Silicon Sea Belt Fukuoka Project

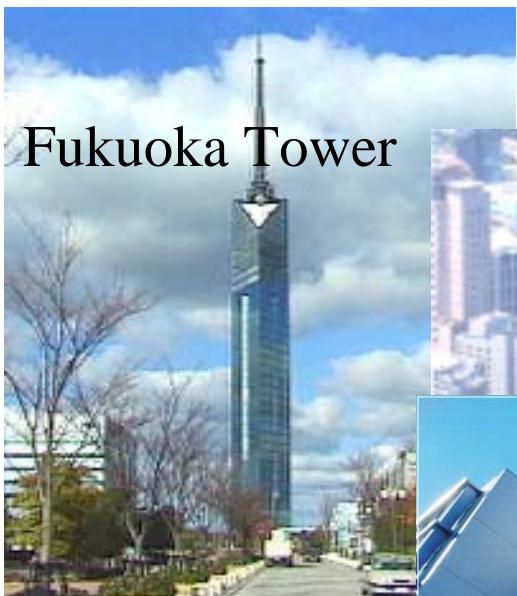
- * Center of Semiconductor design.
- * Semiconductor Industry: Driving force for the growth.
- * Fukuoka is addressing to establish a center of Excellence for SoC design in this area.
- * Conventional Semiconductor Industry (Memory, Processor)-System LSI
- * System LSI is expected to generate the higher added value to the cluster of related industry.



- Silicon Sea Belt Fukuoka Project
- * World production: 50%
 - * Large consumption region



Fukuoka Soft Research Park



Fukuoka Tower

Momochi Hama District



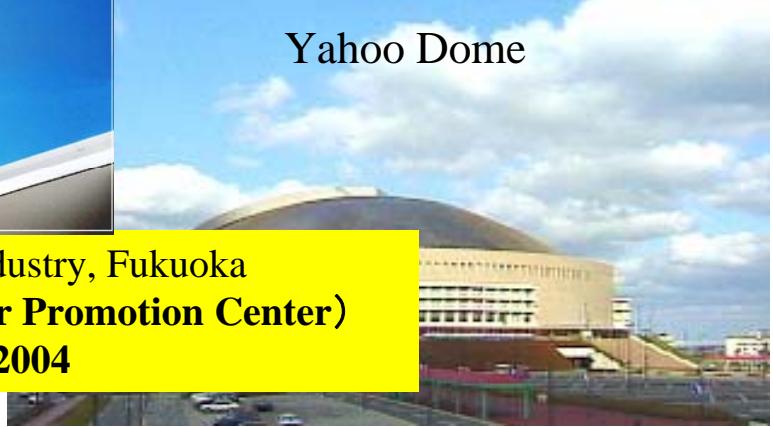
SRP Center Building



Institute of System LSI Design Industry, Fukuoka
(Kyushu University:Entrepreneur Promotion Center)
Established on 2004

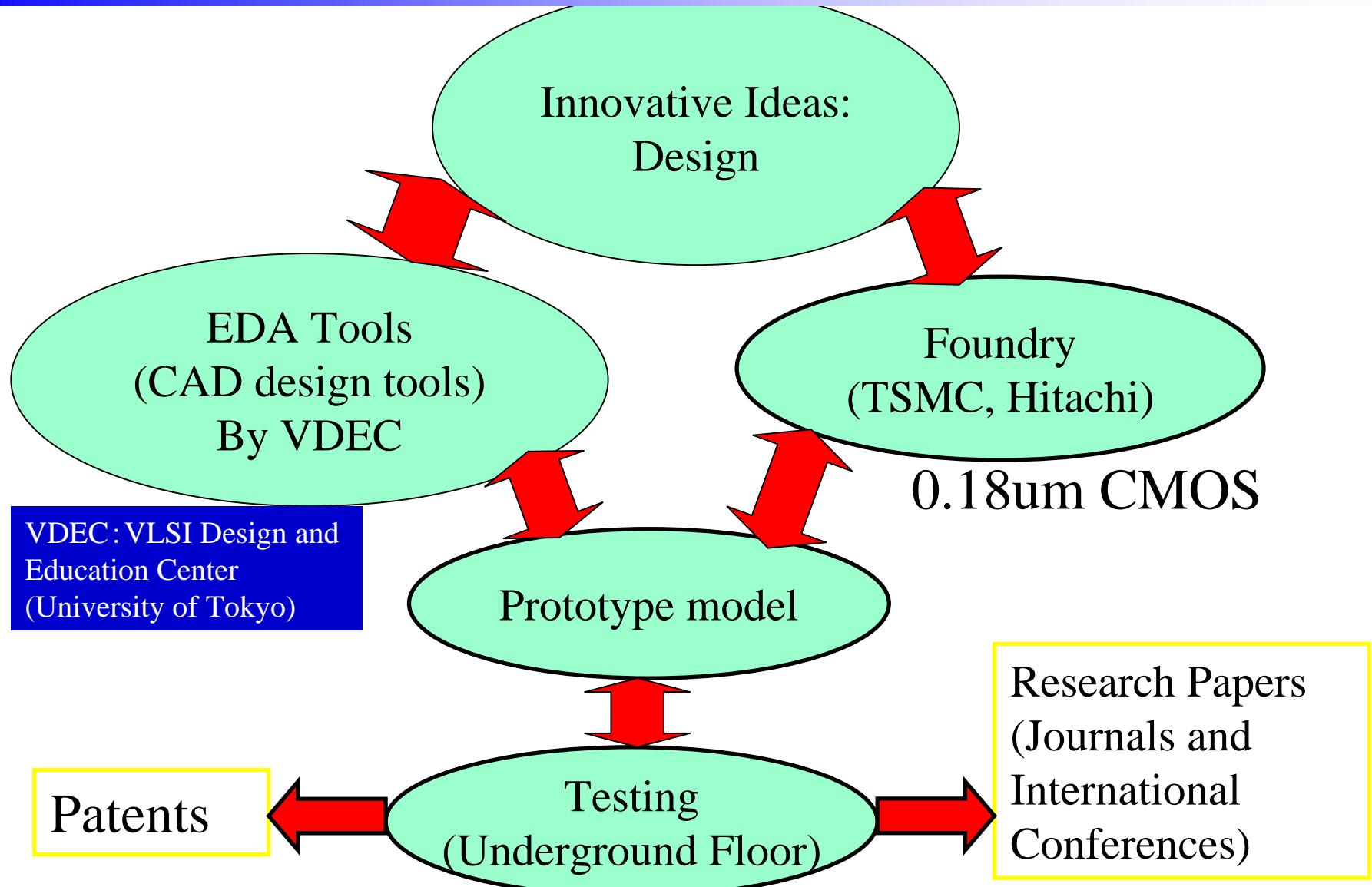


Yahoo Dome

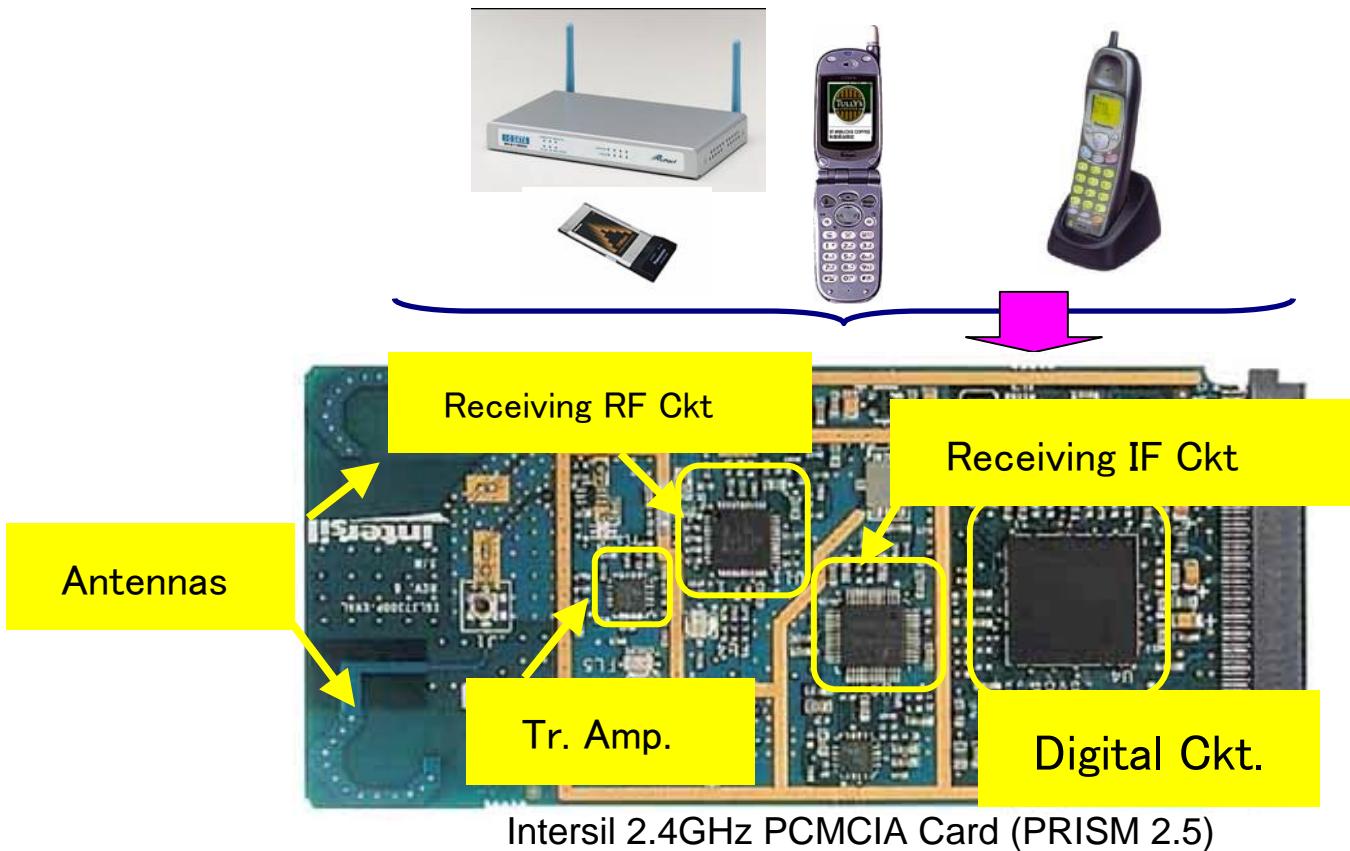


World Class Companies of Japan and Korea:Toshiba, Sony etc

System LSI Research and Development



Prof. Yoshida's Lab Introduction

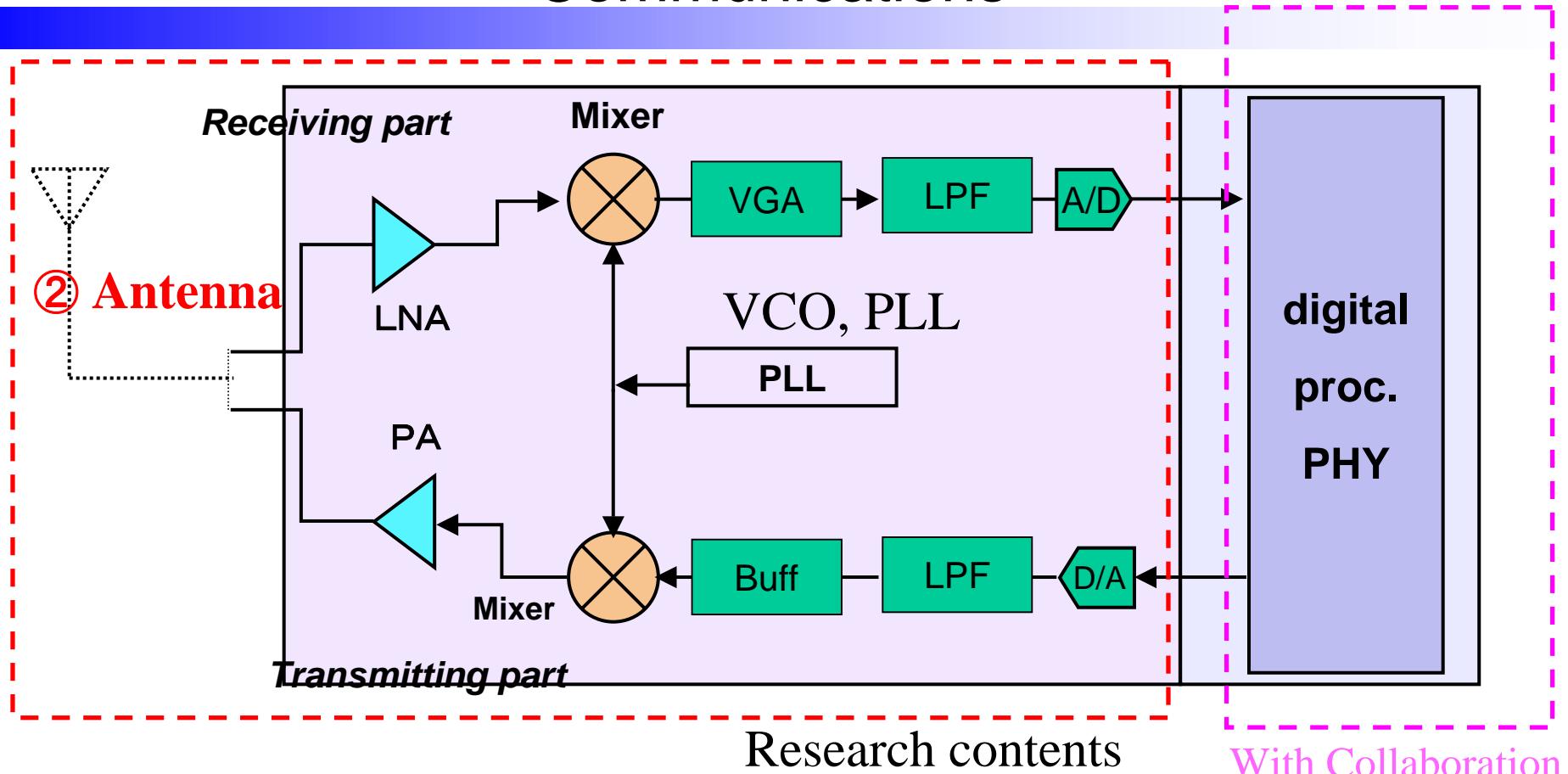


Key Words of Our Research

Miniaturization & Low Power

- ⇒ ① SoC (System on Chip)
- ⇒ ② Antenna

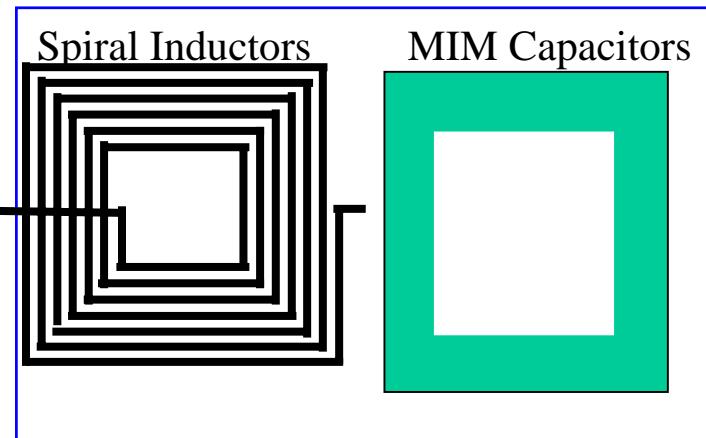
Block diagram of CMOS-LSI for Wireless Communications



① 1-Chip:SoC Implementation (System on Chip)

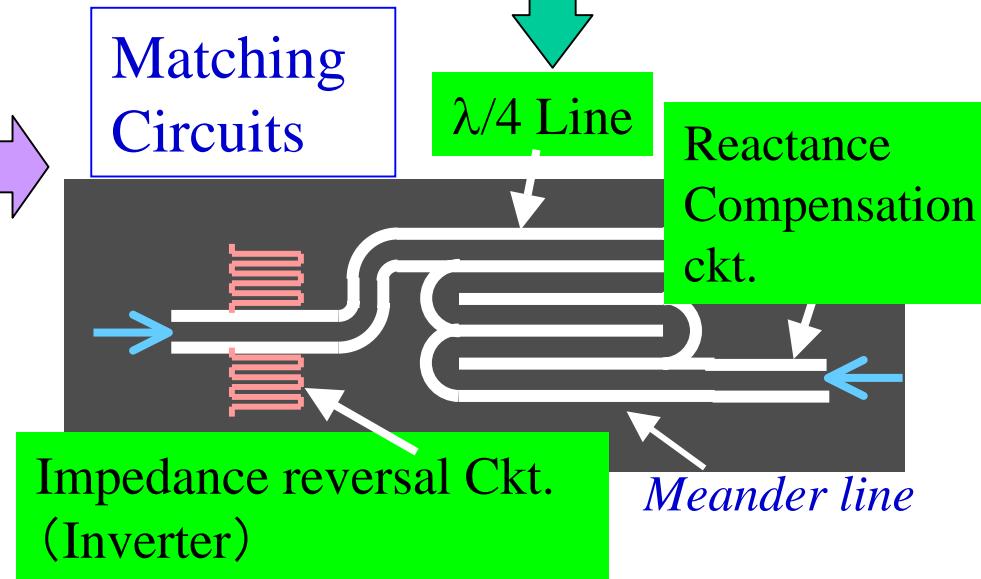
① Proposal of New Design Methodologies for RF Parts

Lump Elements



Spice Models

Transmission line

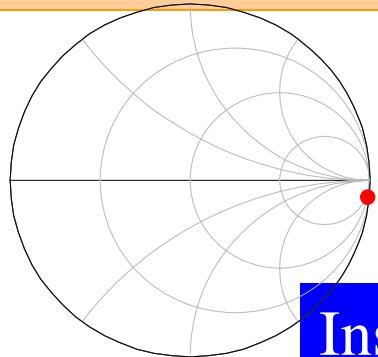


Freedom of Design

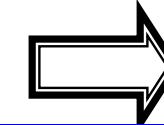
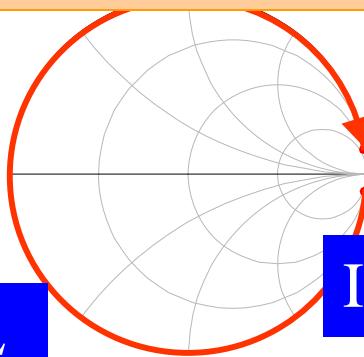
- Size is about 40% and the shape can be adjusted to exploit the vacant space in the chip.

Matching by Lumped Elements

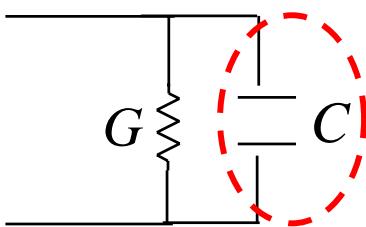
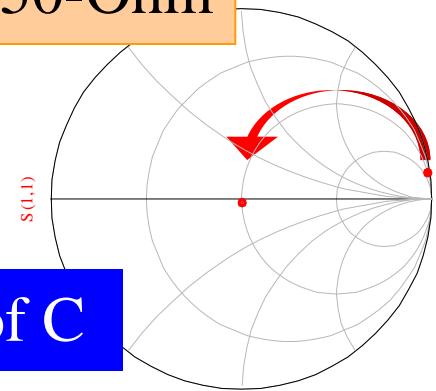
High Impedance (Say: $100-j1000$) Ohm is matched to 50-Ohm



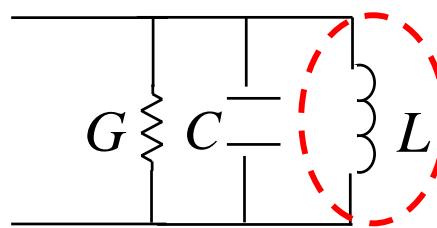
Insertion of L



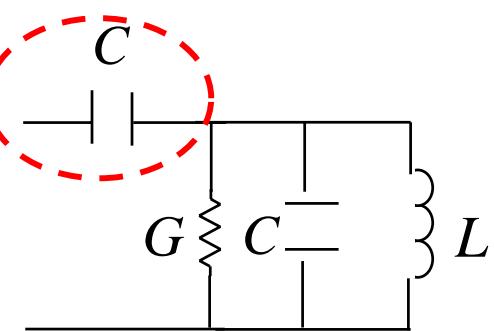
Insertion of C



Very small C

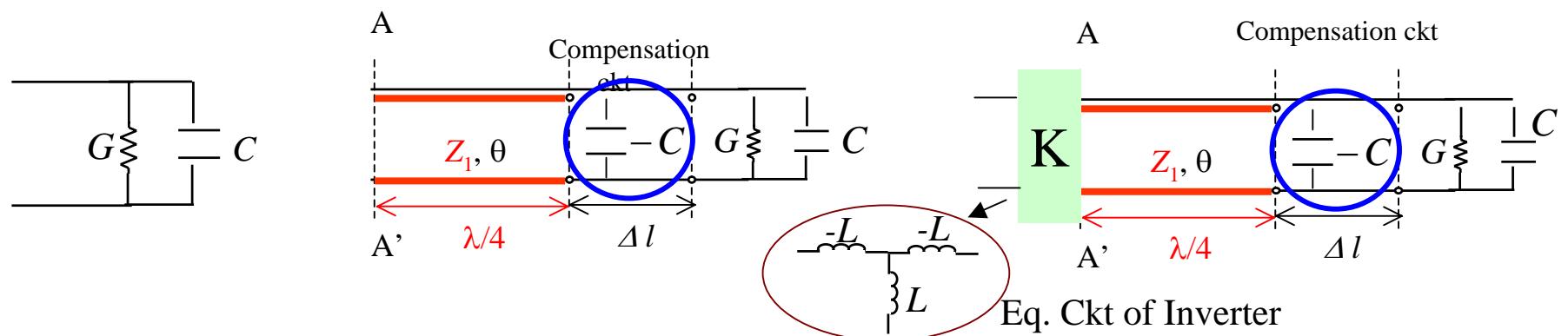
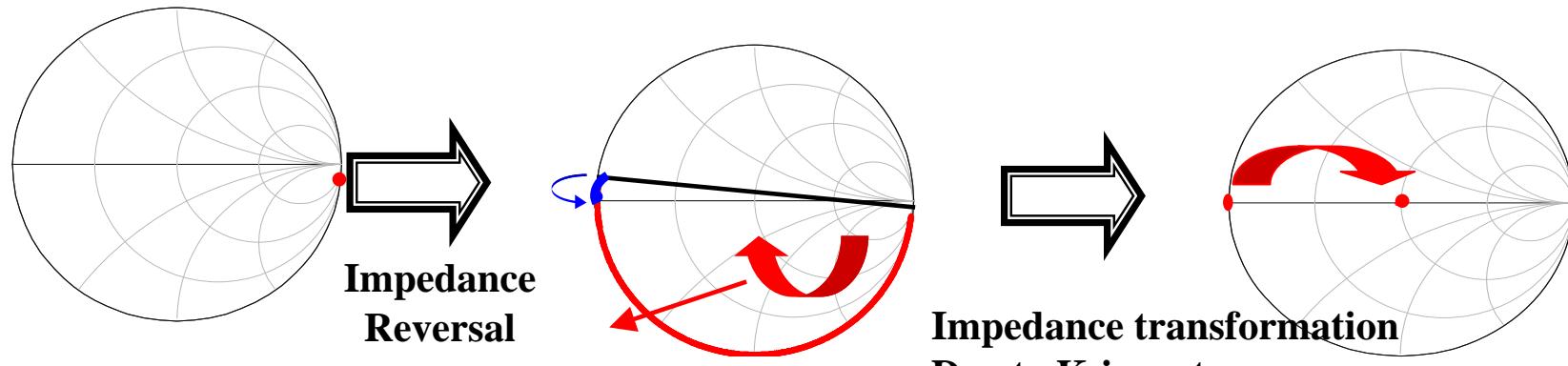


High L is necessary.



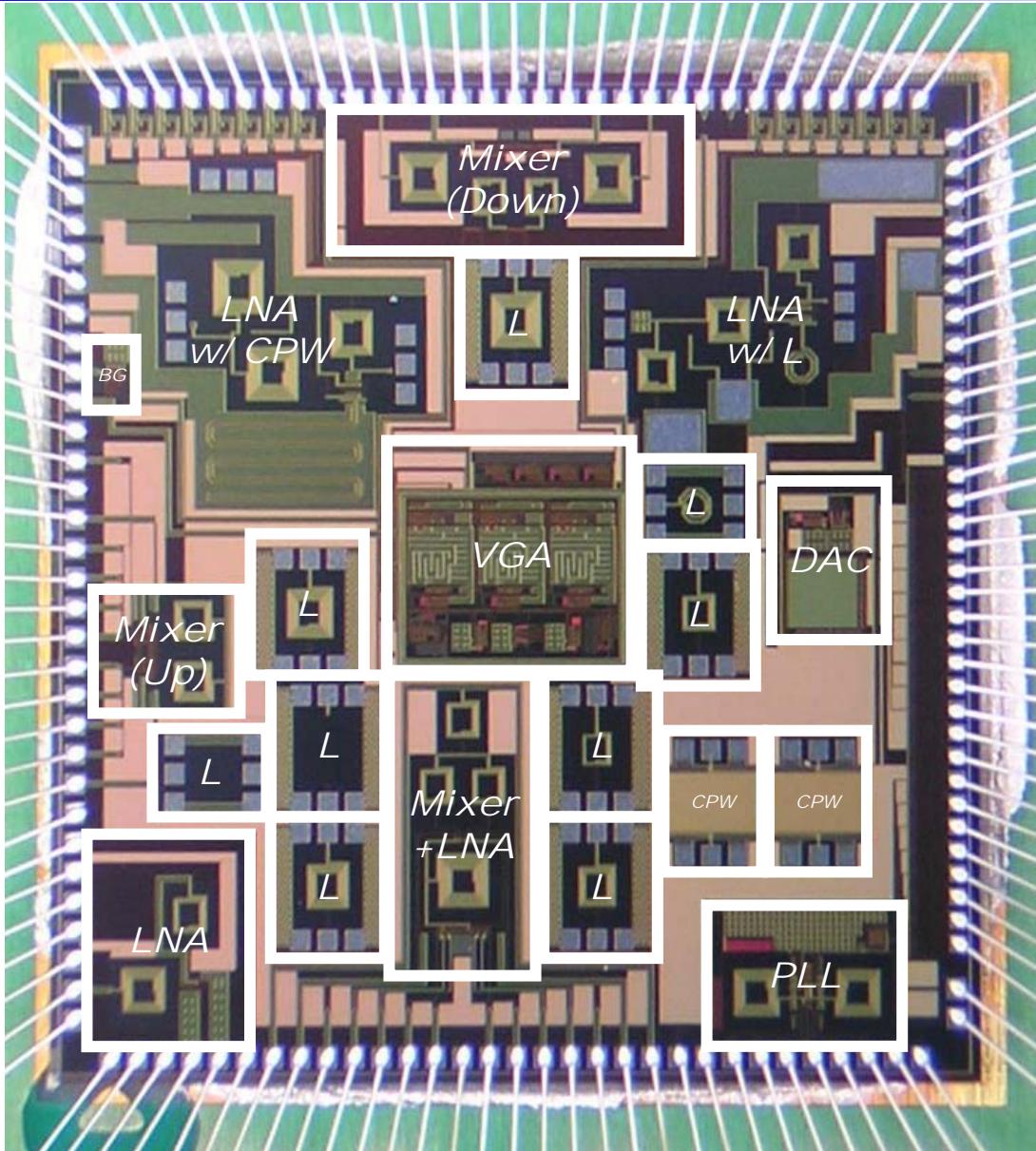
Insertion of Series C
(0.09pF)

Theory of Matching Circuit



➤ Presented at IEEE RFIC2006.

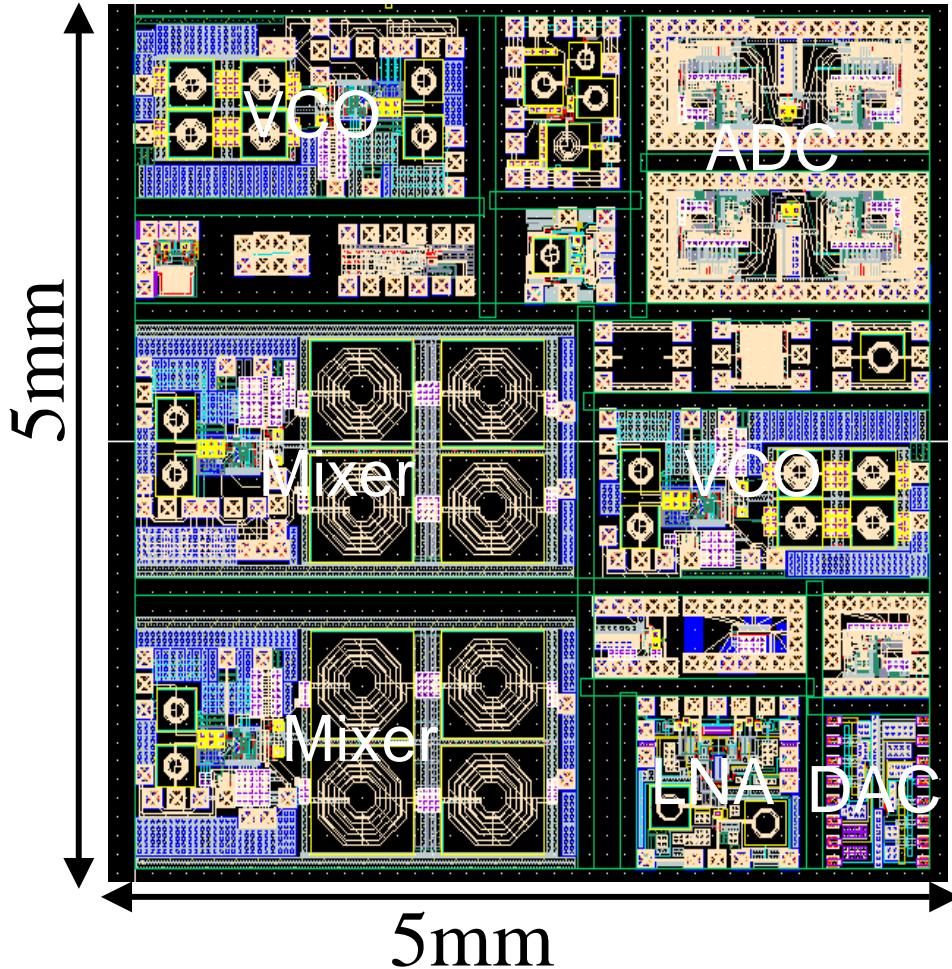
Prototype Design [I]



TSMC 0.25 μ m CMOS (1P5M)
Chip size=5mm x 5mm

- LNA; Cascade, w/ CPW, w/ L
- Mixer; Up, Down
- **Down Mx +LNA**
- PLL
- BG
- VGA
- DAC
- Inductor TEG
- CPW TEG

Prototype Design [II]



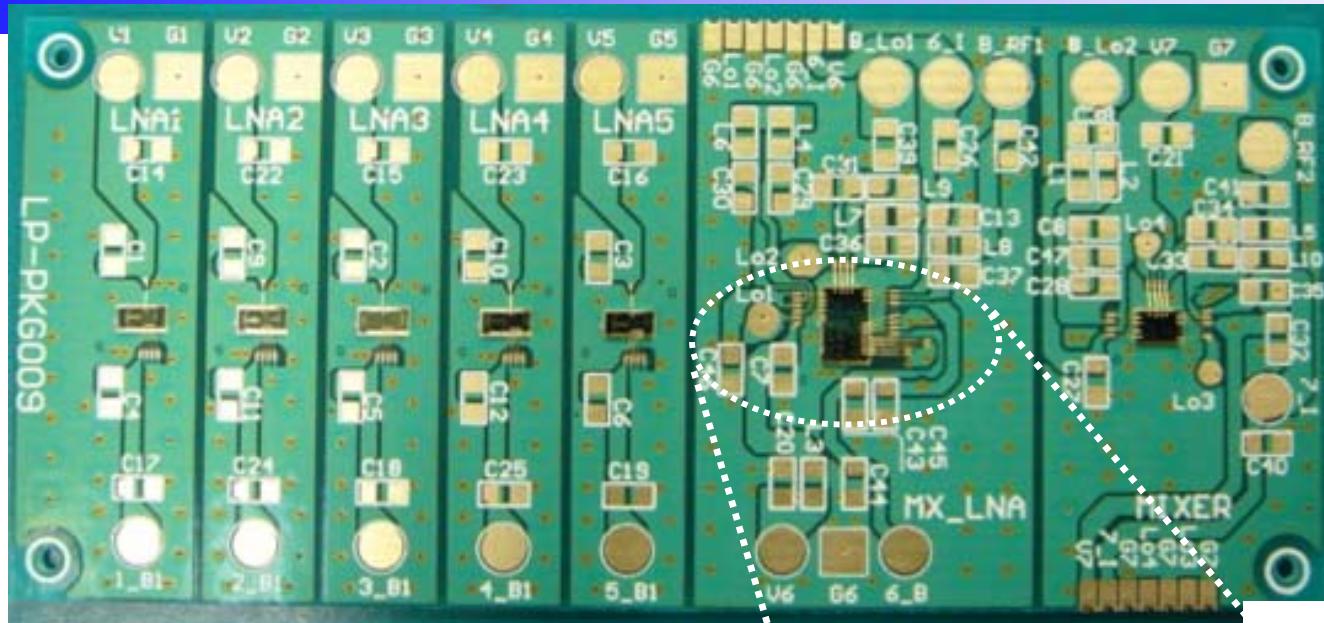
TSMC 0.18 μ m CMOS (1P6M)
Chip size=5mm x 5mm

- UWB-LNA, mixer, ADC, DAC
- Test chips.

For MIMO-MESH Project

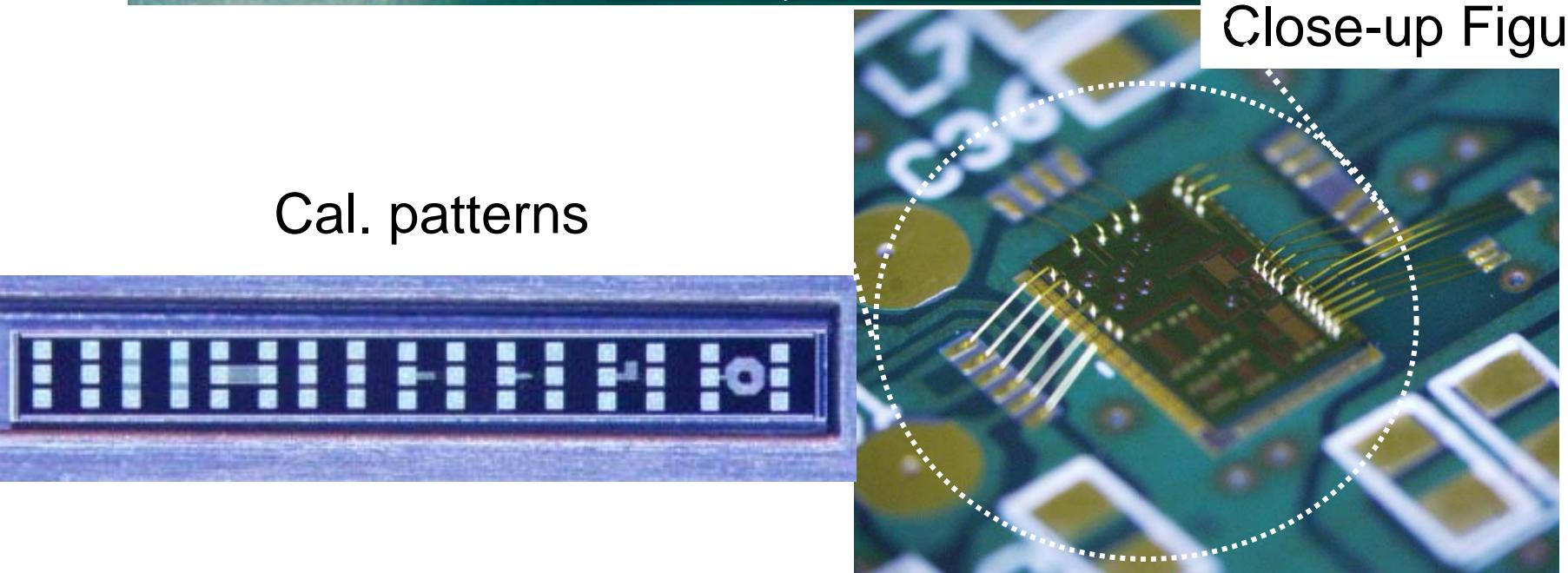
- Mixer, VCO, 1-bit ADC

TEG Chip Photo



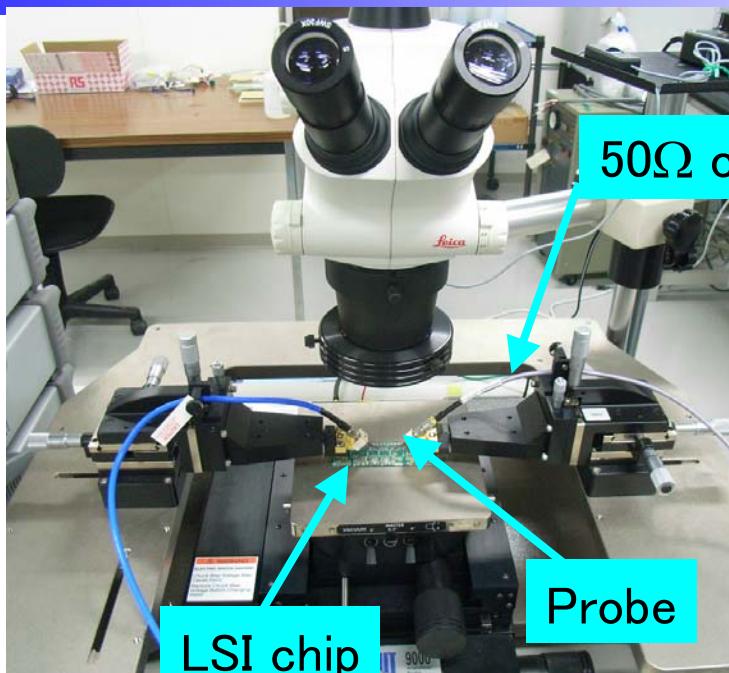
PKG
Substrate

Close-up Figure

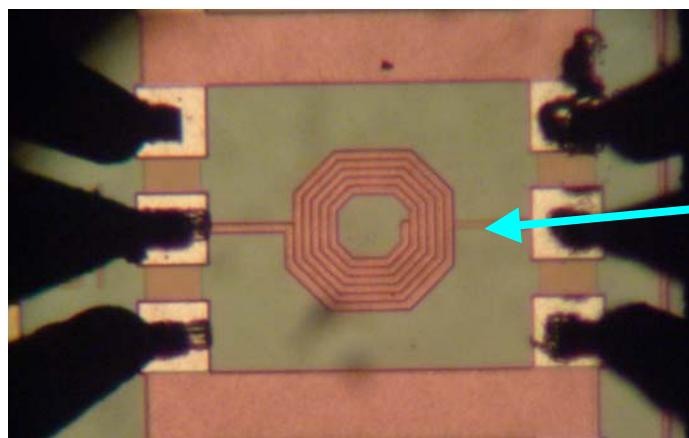


Cal. patterns

Lab Facilities of Testing



Air Coplanar Probe



Spiral inductor

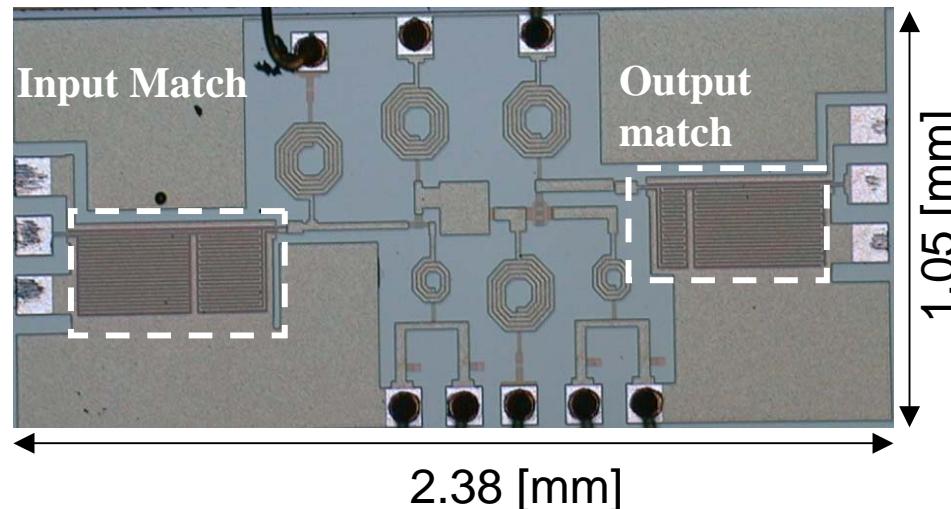
Results [1]

- Power Amp. (IEEE .11b)
- LNA (UWB)
- VCO & DCO (IEEE .11a)
- LNA + Mixer (IEEE .11b)
- Ring Oscillator

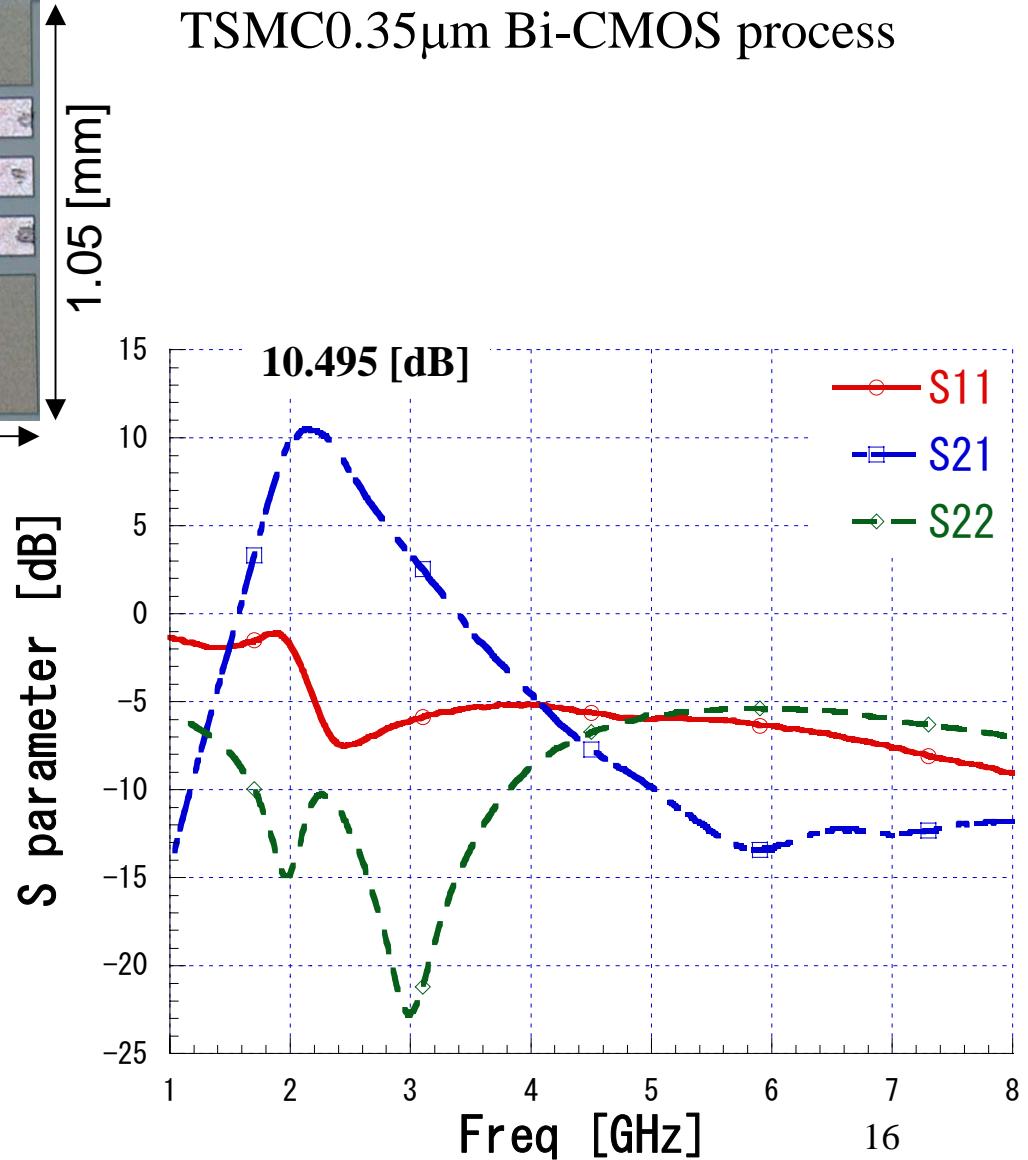
TSMC:

0.35um Bi-CMOS, 0.25um CMOS &
0.18um CMOS

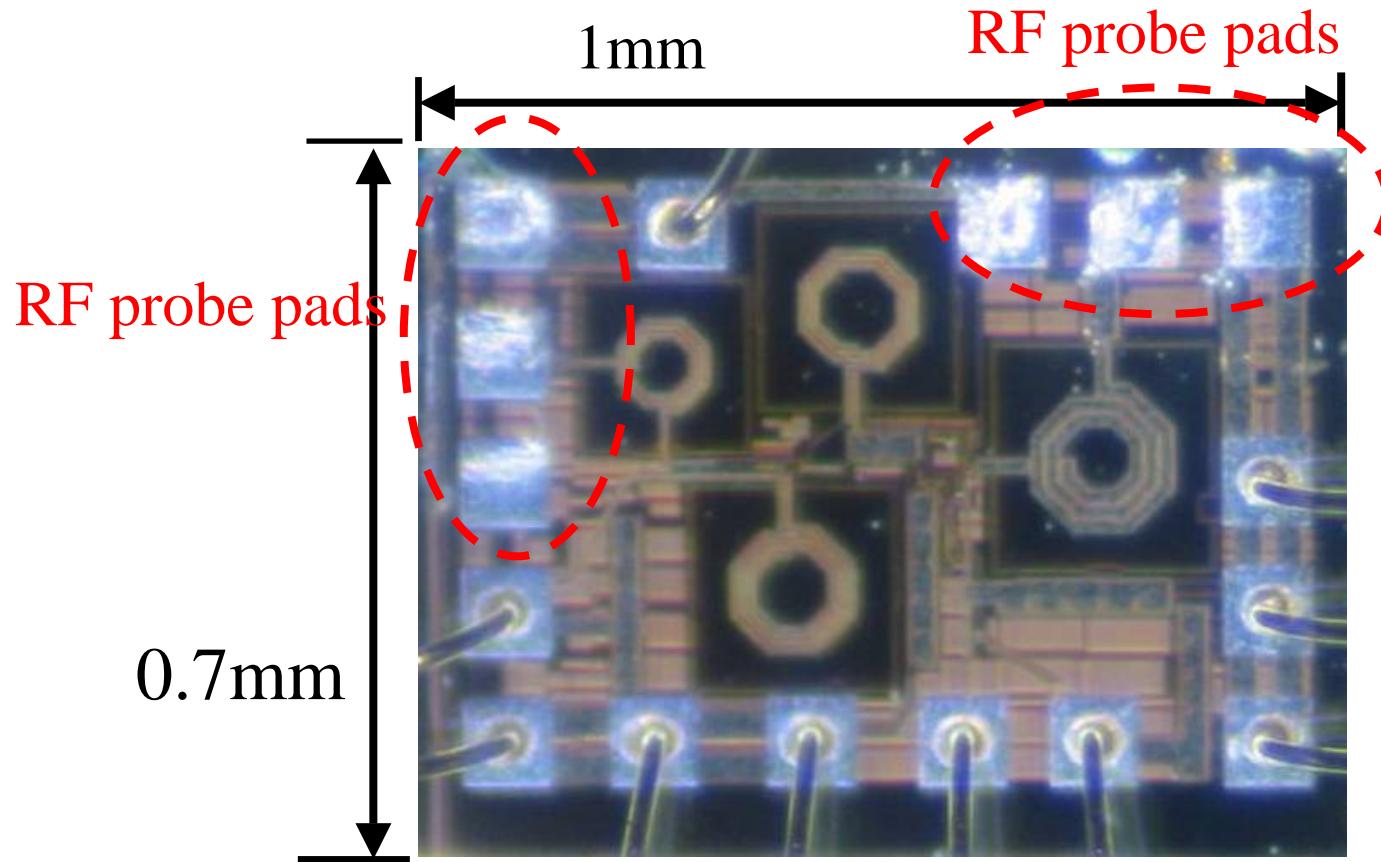
Power Amp.



TSMC0.35μm Bi-CMOS process

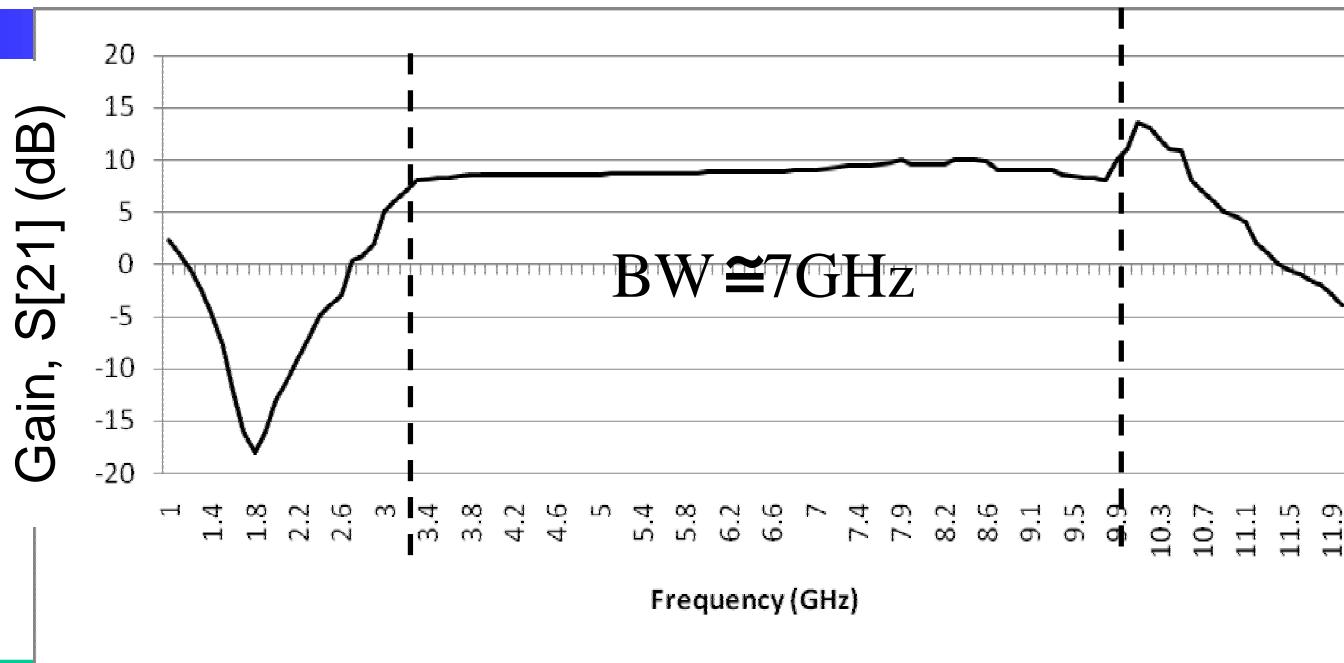


Ultra wideband (UWB) Low noise Amp. (LNA)



Chip photo of the designed UWB LNA in 0.18um CMOS.

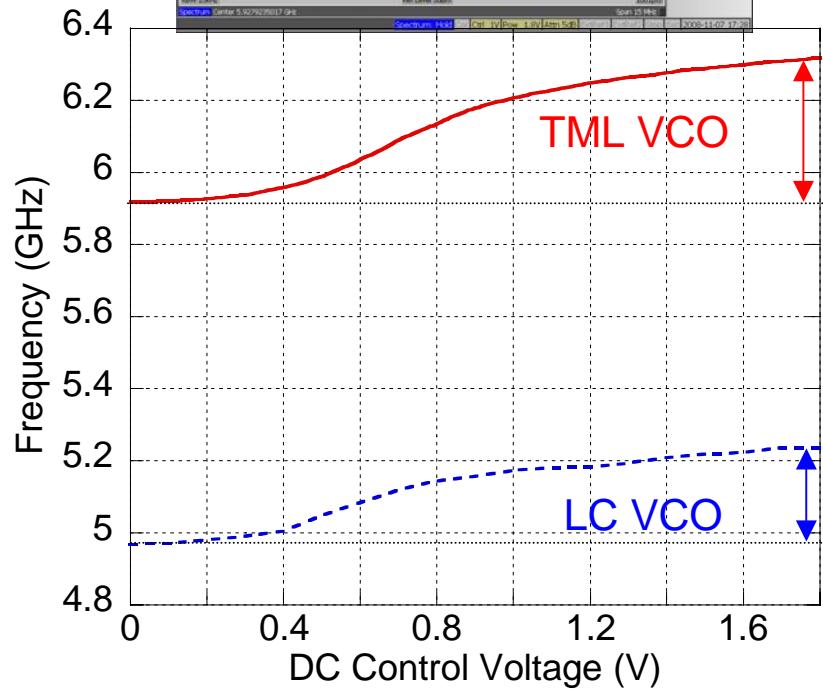
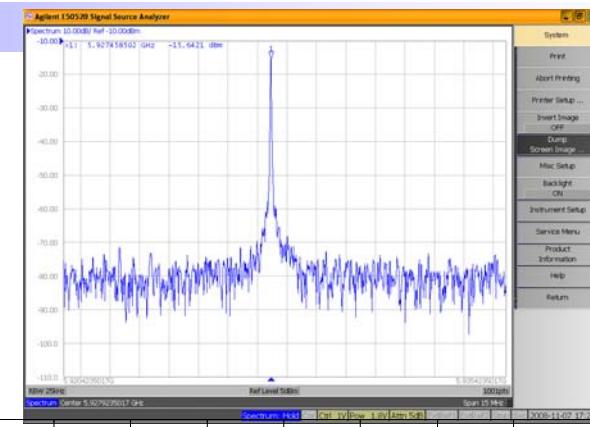
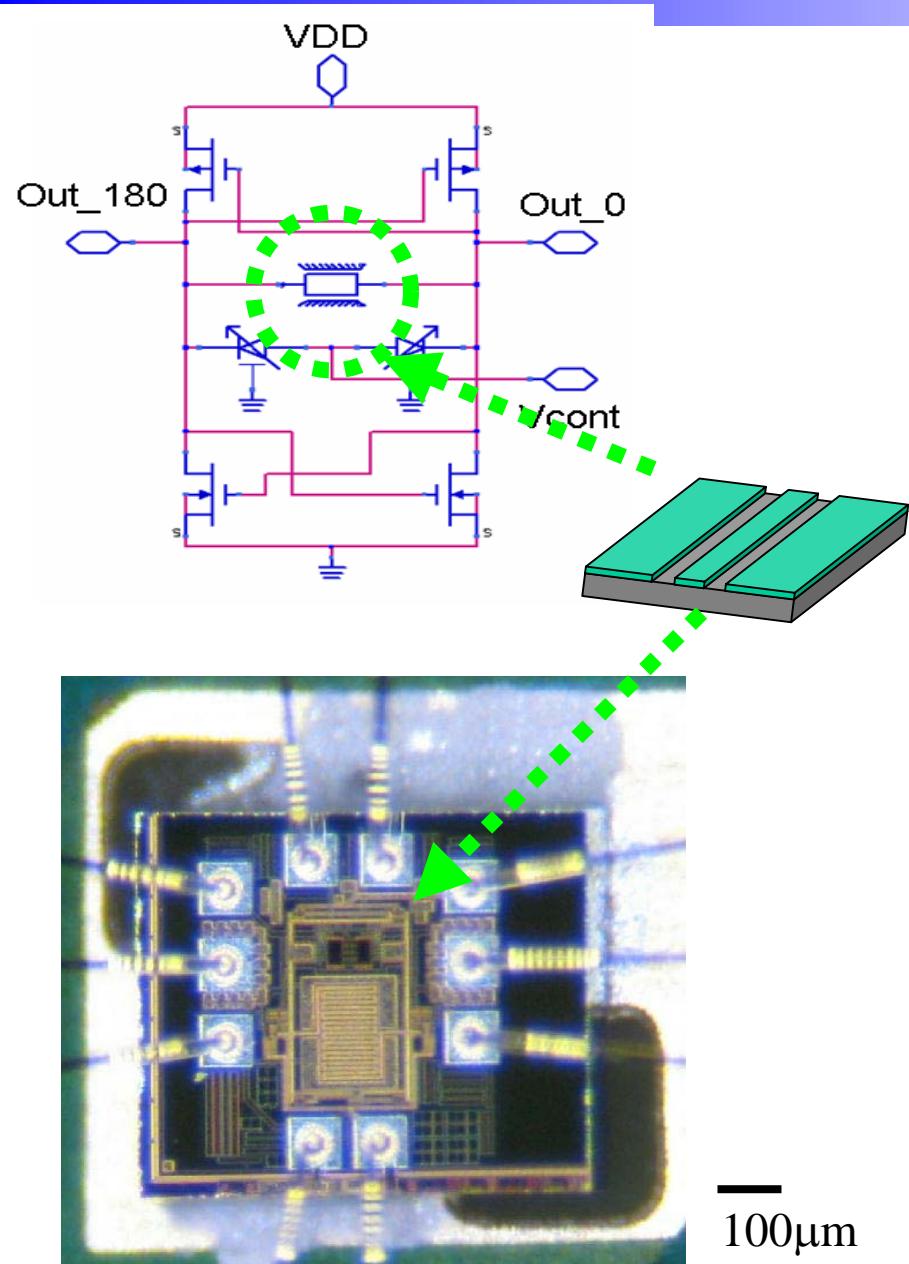
Measurement results



Reference	S21	NF(dB)	S11 (dB)	Freq. (GHz)	IIP3 (dBm)	Technology
JSSC[1]	9.7~7	4.5~5.1	<-11	3.1~10.6	-6.2	0.18μm CMOS
JSSC [2]	13	3.3 (max 6.5)	<-7	2~10	-7	0.18μm BiCMOS
Ref. [3]	9.5	5 (max 5.6)	<-10	3-11	-13	0.18μm CMOS
This work (Post-layout)	16.5 (flat)	<3.7 (flat)	<-9	3.1~10.6	-8	0.18μm CMOS

-> Presented at IEEJ Analog VLSI symposium, Aug, 2008.

VCO (Voltage controlled Osc.) with TML



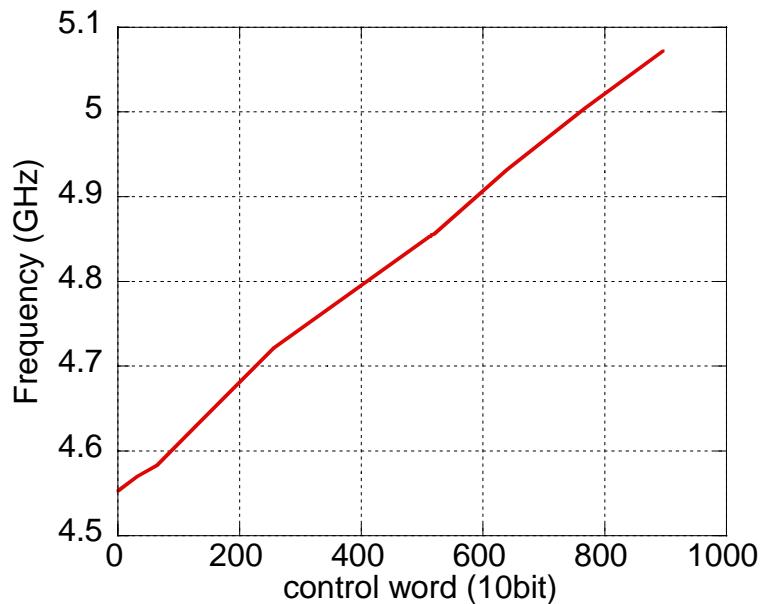
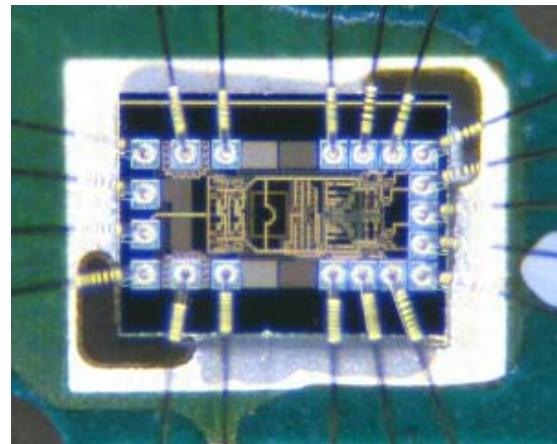
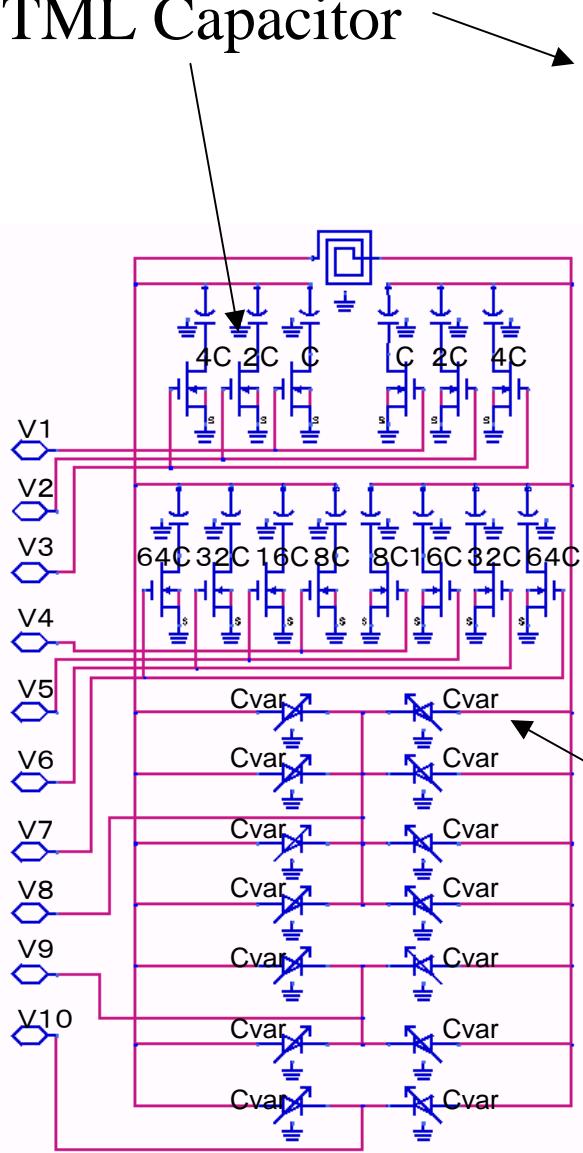
TML VCO = -112 dBc/Hz @ 1MHz
LC VCO = -110 dBc/Hz @ 1MHz

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TSMC 0.18 μm CMOS process

LC-DCO (Digitally controlled OSC)

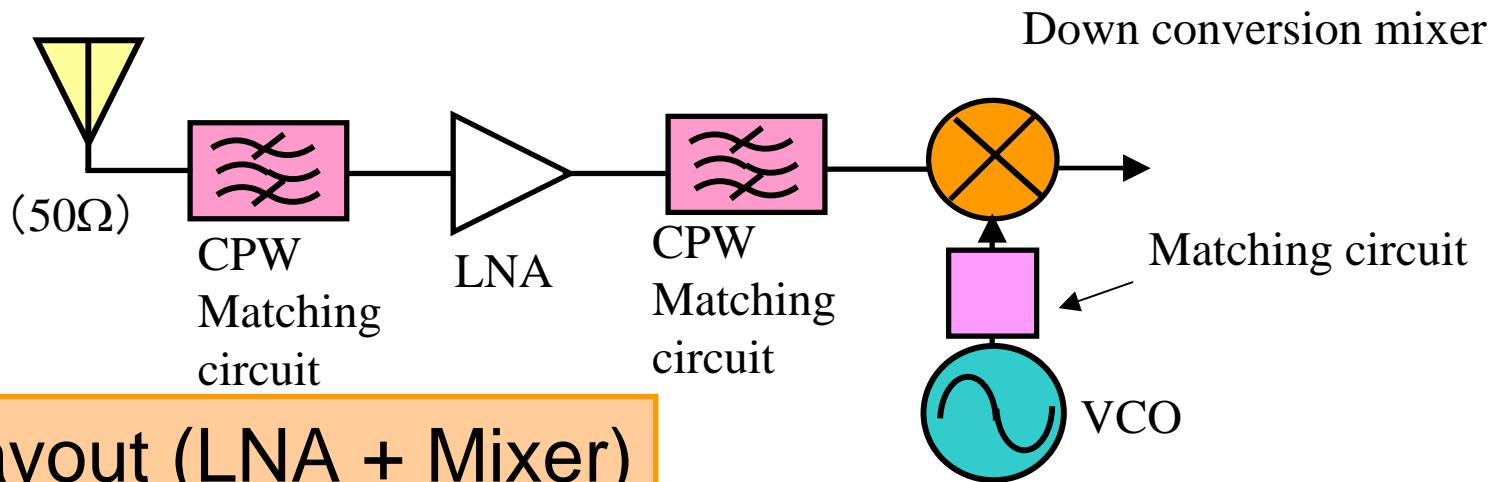
TML Capacitor



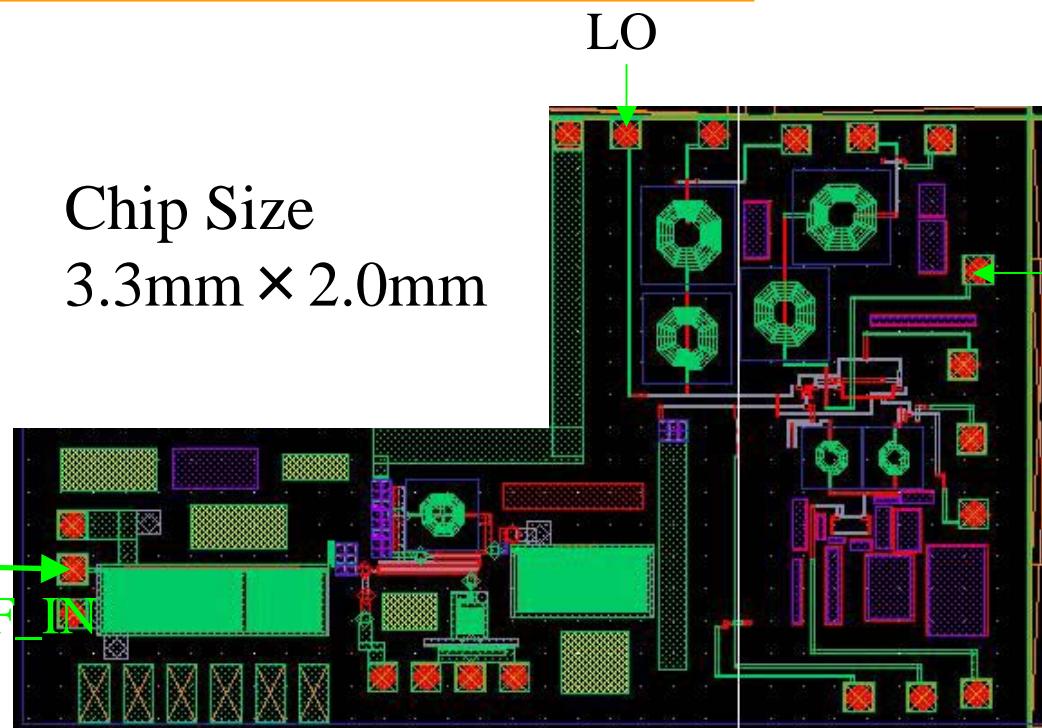
LC VCO= -119dBc/Hz @1MHz
20

TSMC0.18μm CMOS process

LNA + Mixer (Down converter)



Layout (LNA + Mixer)



Chip Size
 $3.3\text{mm} \times 2.0\text{mm}$

Size
Lumped element TML

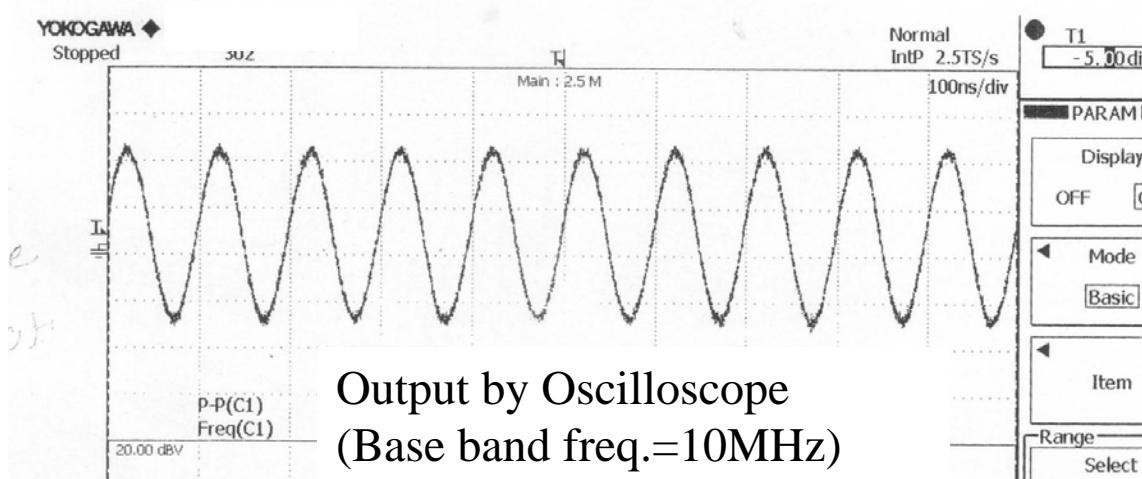
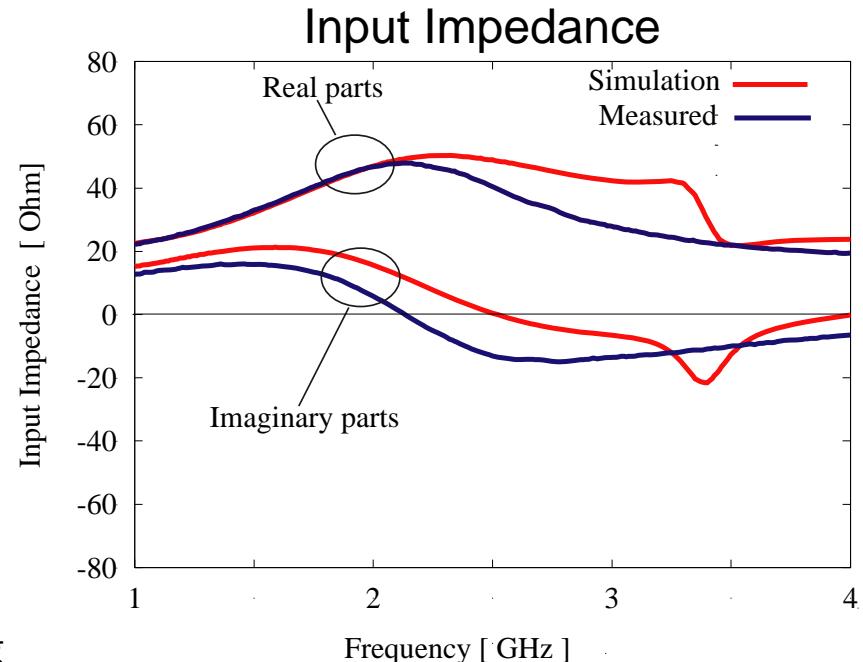
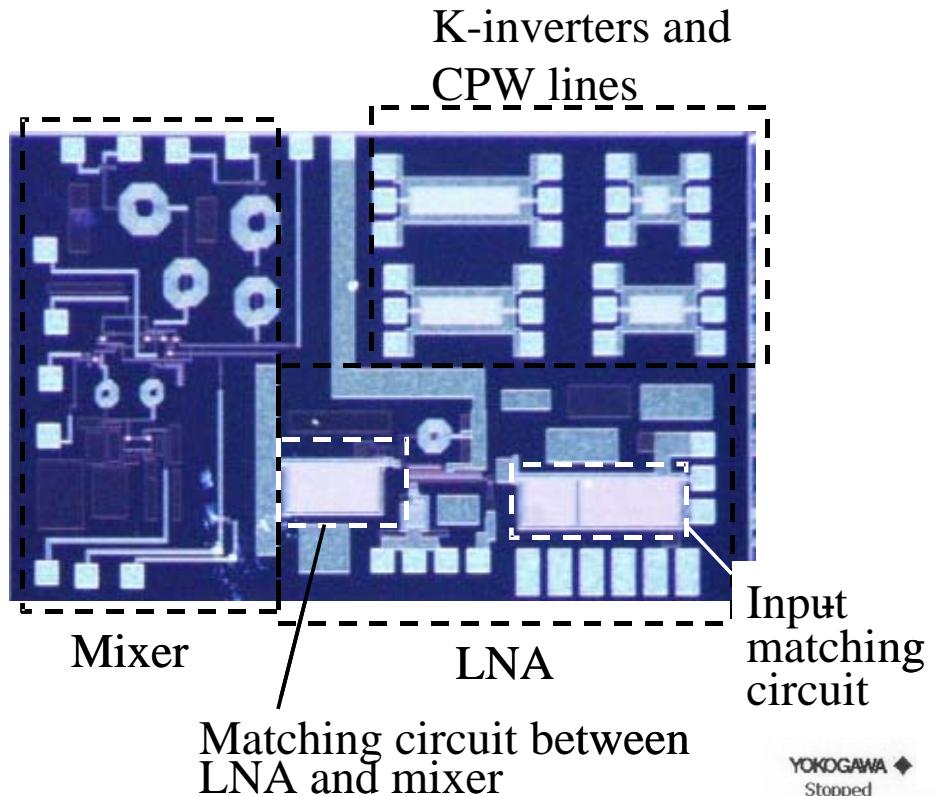


$480\ \mu\text{m} \times 250\ \mu\text{m}$
 $600\ \mu\text{m} \times 300\ \mu\text{m}$
(約 14.0nH @ 2.45GHz)



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LNA + Mixer (Down converter)

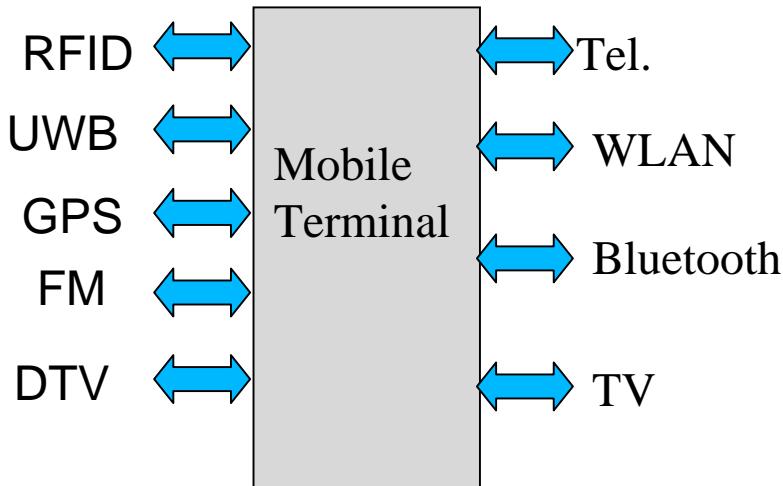


Ring-Oscillator

Demand of Wideband Systems

WLAN(.11a,.11b), WCDMA, GPS, PHS, GSM, IMT2000 ...

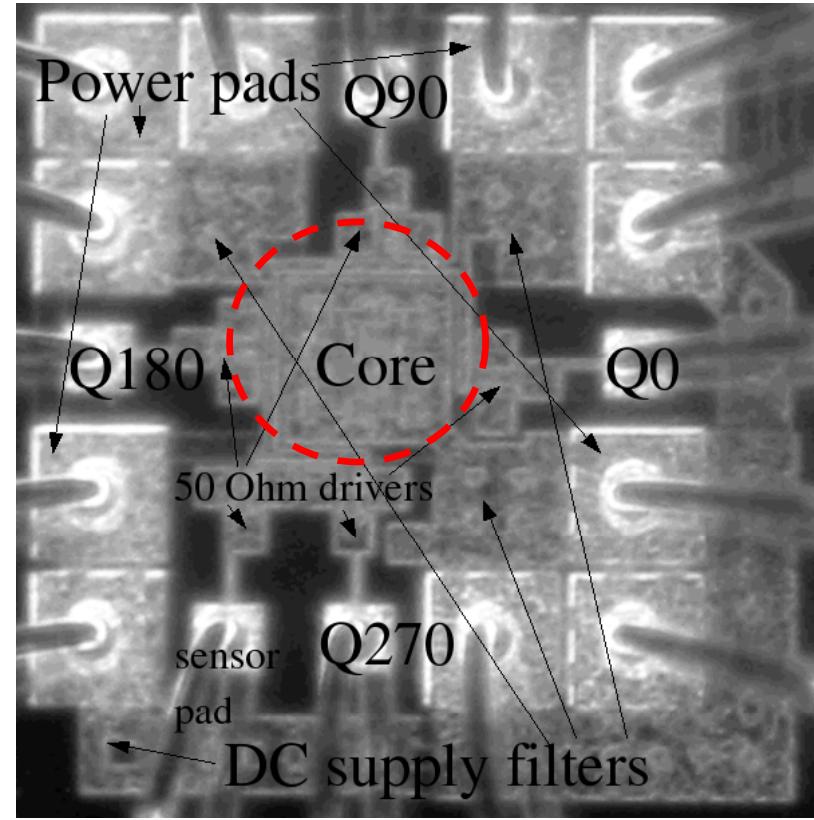
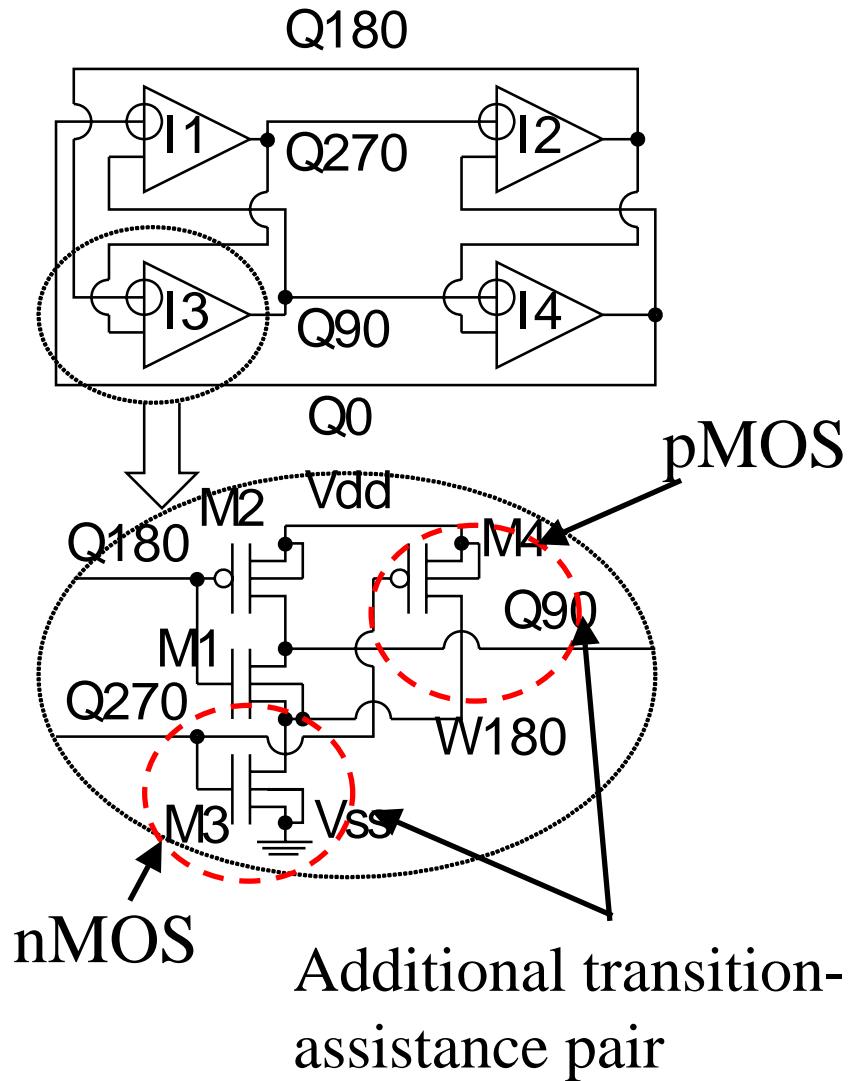
- Reconfigureable RF circuit.
- Multi-standard systems in one terminal.



Proposed Quadrature Ring Oscillator

Chip photo

TSMC 0.18um CMOS Process



Size: 0.30 mm² with bonding pads.

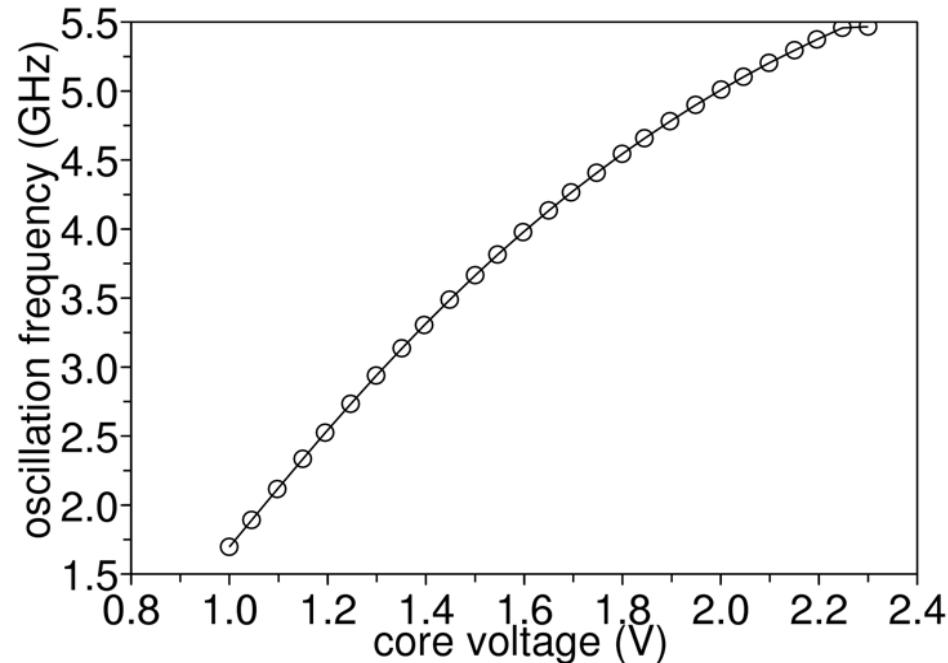
Size: 0.01 mm² without bonding pads.

Measurement results

Time-Domain



Tuning Range

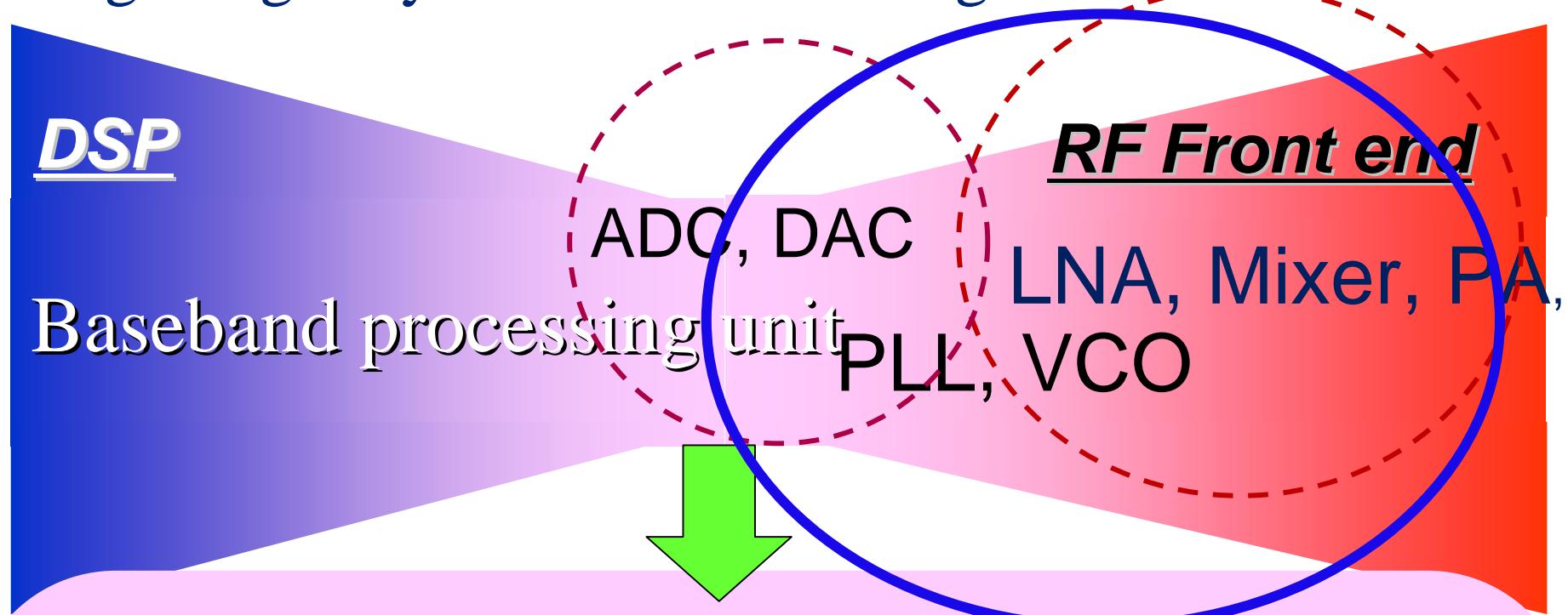


- Tuning Sensitivity = 2.9 MHz/mV
- Tuning range = 1.7 GHz ~5.5 GHz
- FOM= -162.2 dBc/Hz

Figure of Merit: $FOM = -20 \log\left(\frac{F_{osc}}{F_{off}}\right) + PN + 10 \log\left(\frac{P_{diss}}{0.001}\right)$

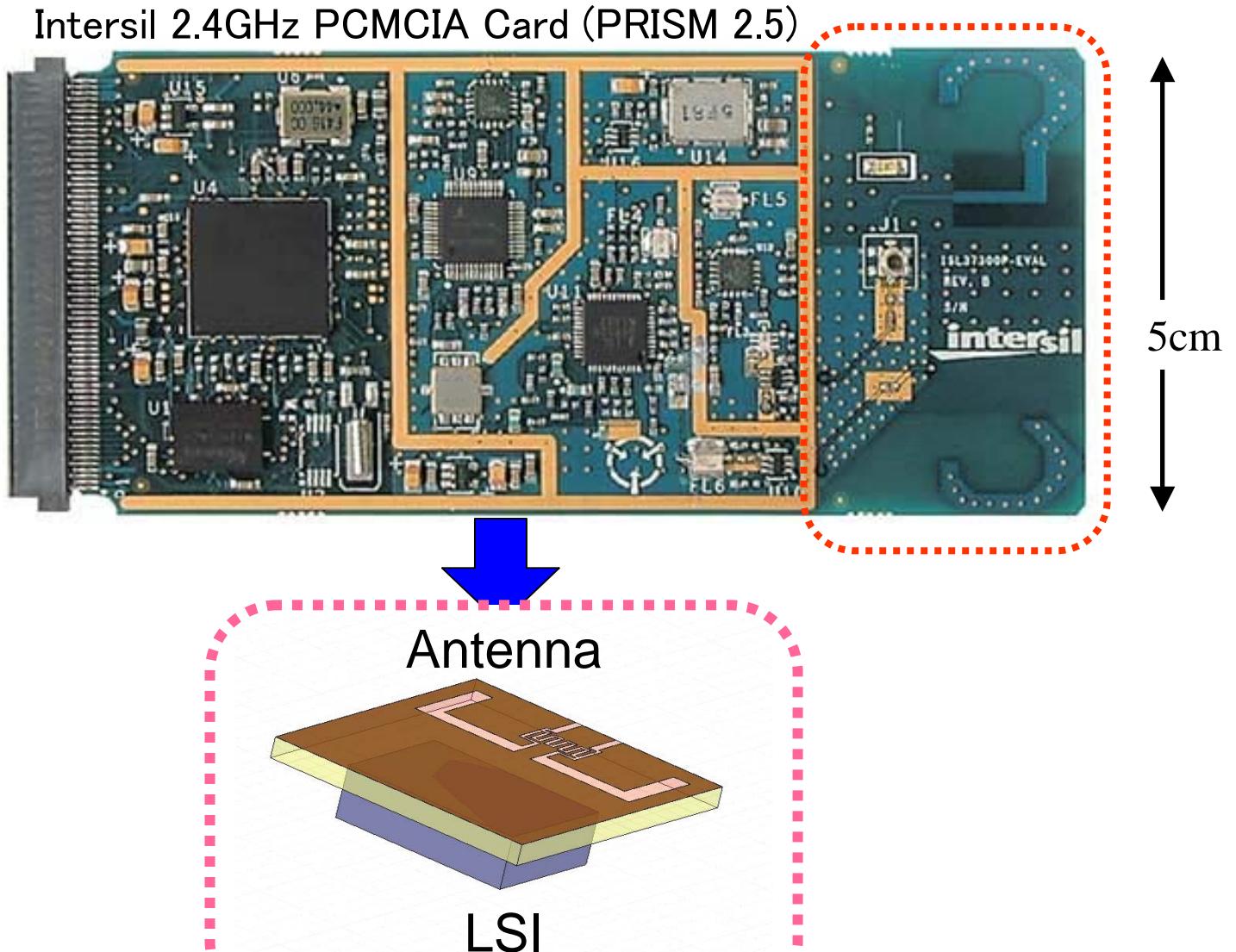
Wireless System LSI

Digital techniques: a New Concept in RF circuit design:Digitally-assisted RF/Analog



*Key word: RFIC (Digitally-assisted
RF/Analog)*

② Development of Miniaturized Integrated Antennas



Small size, thinner and one-sided directional antennas are necessary!

Antenna Applications

- *One-sided directional antenna*

300MHz, UHF, 2.4GHz (.11b), MIMO (.11a), UWB

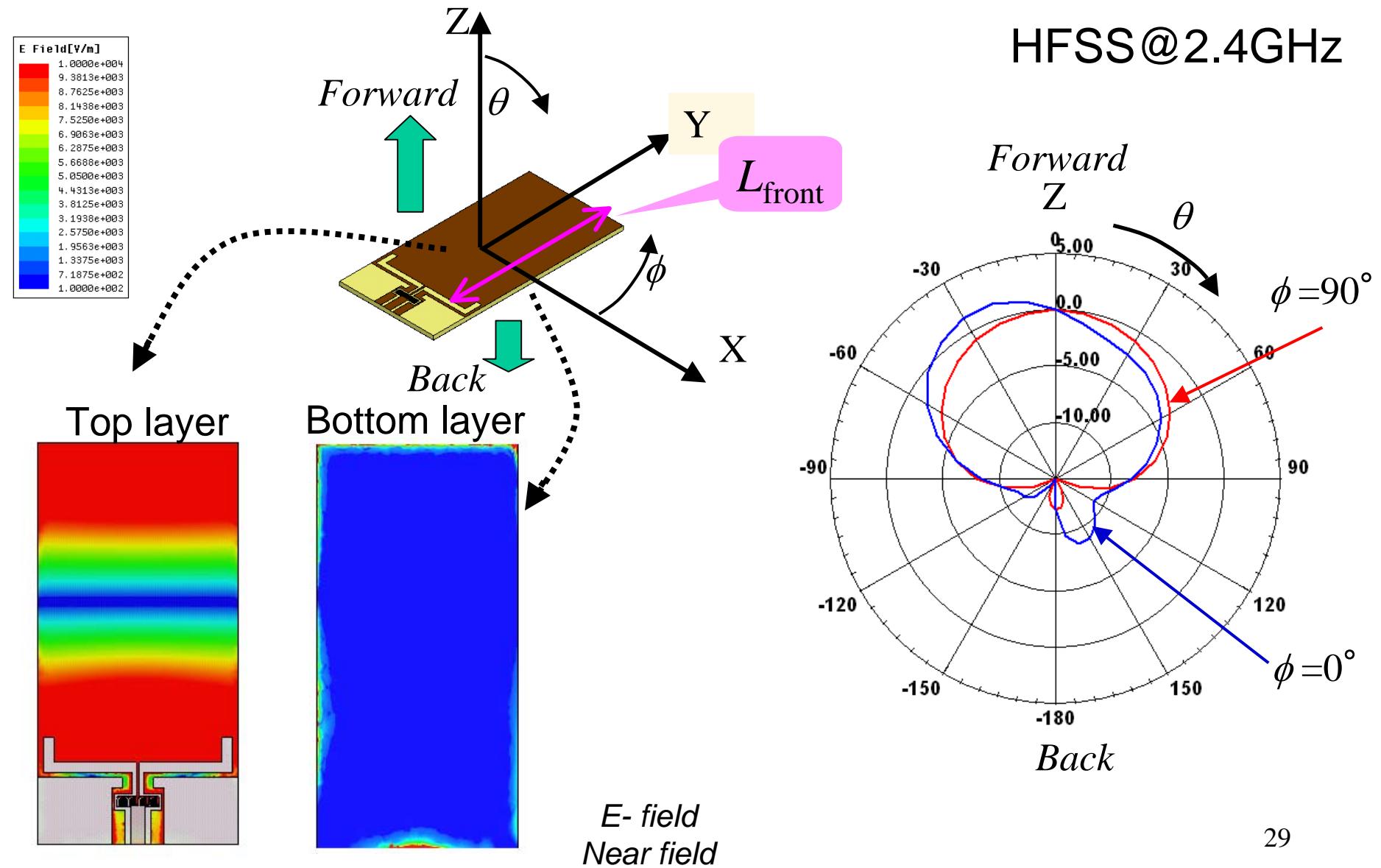
- *Electrically small antenna with matching circuit*

UHF, 2.4GHz, 5GHz

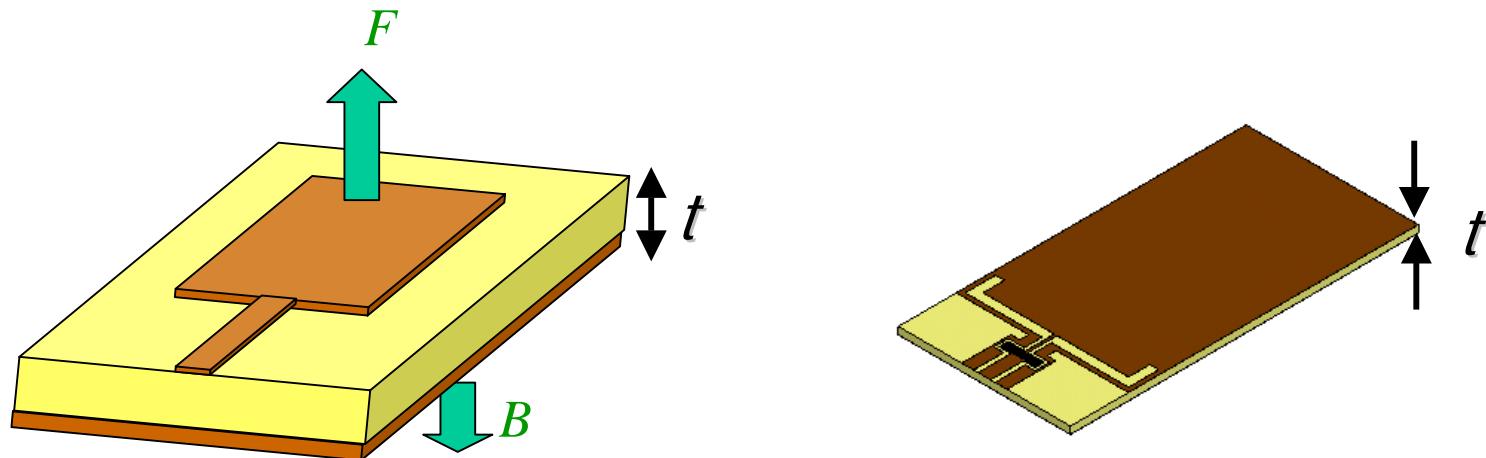
- *Dual band antenna*

PDC + 3G (800MHz + 2GHz)

Simulated field pattern and radiation pattern of the one-sided directional antenna



Advantages of Proposed Theory: Gain can be realizable at thinner Substrate



	Thickness of the substrate t [mm]	1.6	0.8	0.4
One-sided slot	Gain[dBi]	1.177	0.81	-1.516
Patch antenna	Gain[dBi]	1.254	-1.057	-4.145

A red arrow points from the last column of the table to a circle, indicating the proposed theory's advantage. A black arrow points from the last column to a cross, indicating a conventional design's disadvantage.

....advantage for multiplayer MMIC circuit.

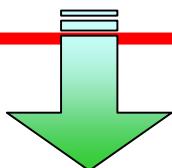
By 3D-EM Simulation

Electrically small antenna (ESA)

An antenna that dimension is much smaller than quarter wavelength...

$$\Rightarrow \text{Antenna length} < \lambda/4$$

- ◆ Small Radiation Resistance
- ◆ Narrow bandwidth
- ◆ Sensitive to the conductor resistance



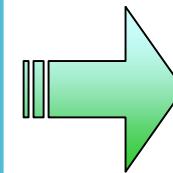
Impedance Matching



Design of Bandwidth



One-Sided
Directional
Antenna

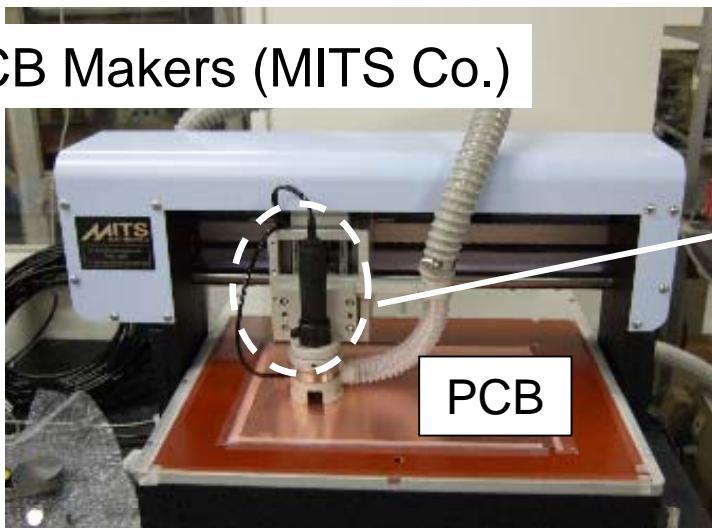


*Proposed
Antenna*

integrates

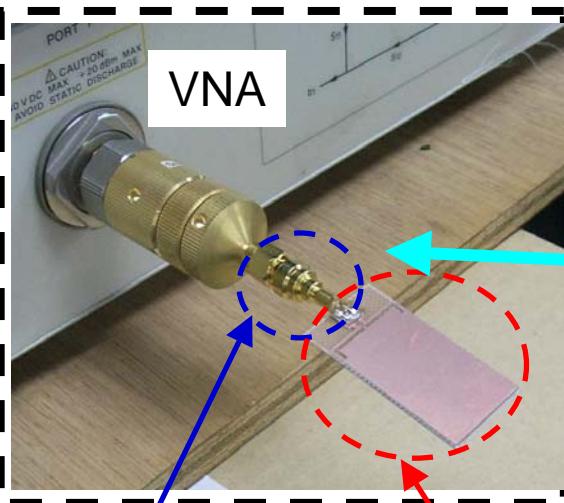
Antenna Fabrication and Measurement System

PCB Makers (MITS Co.)



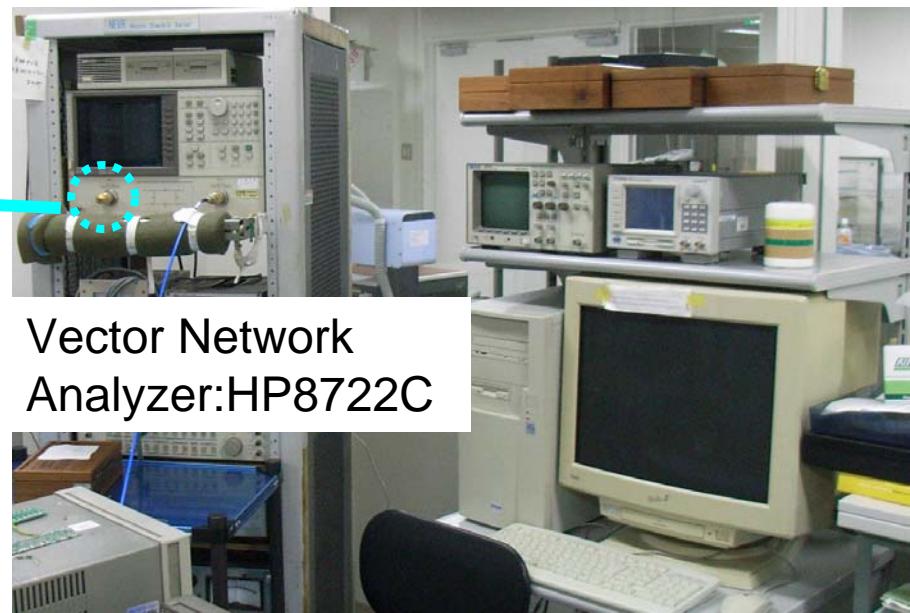
High-frequency
Milling Cutter

VNA



MMCX-SMA
Connector

Antenna

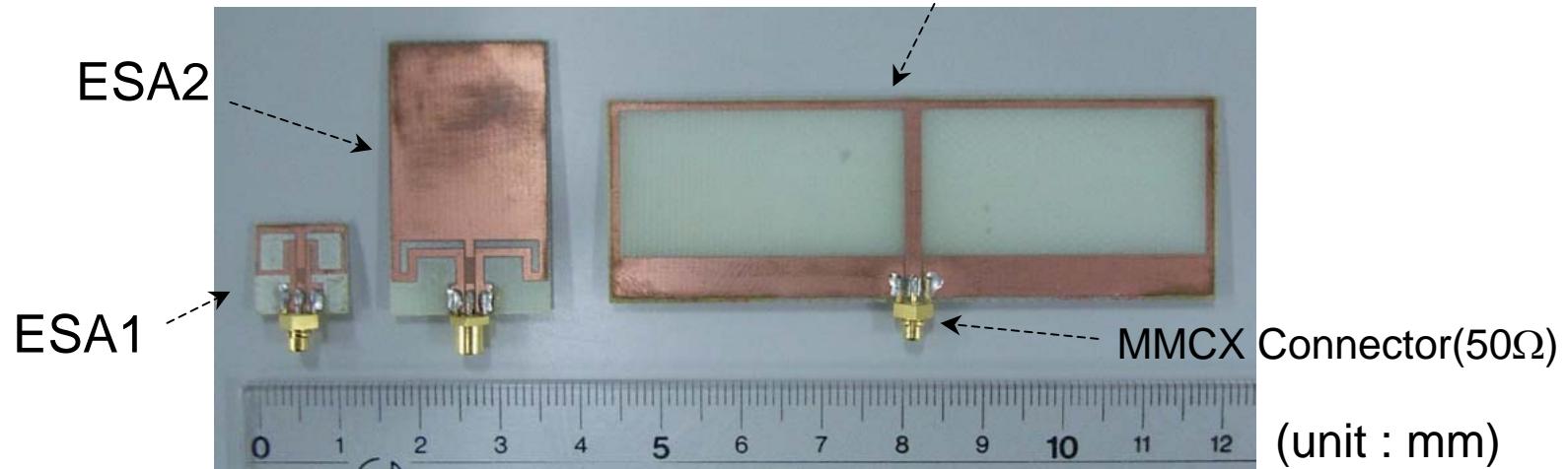


Vector Network
Analyzer:HP8722C

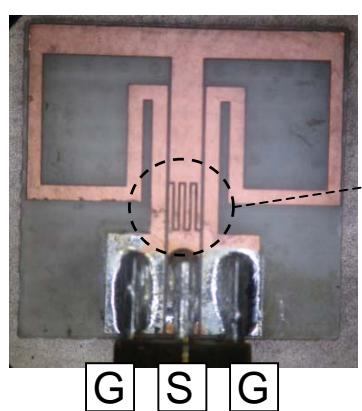
Photograph of the ESAs

Size comparison of the antennas

standard slot dipole antenna
(size:74.0mm × 24.0mm,gain:3.92dBi)



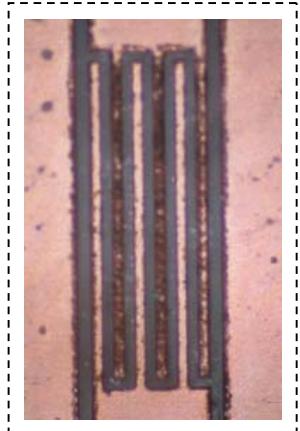
Enlargement of the ESAs



J-inverter

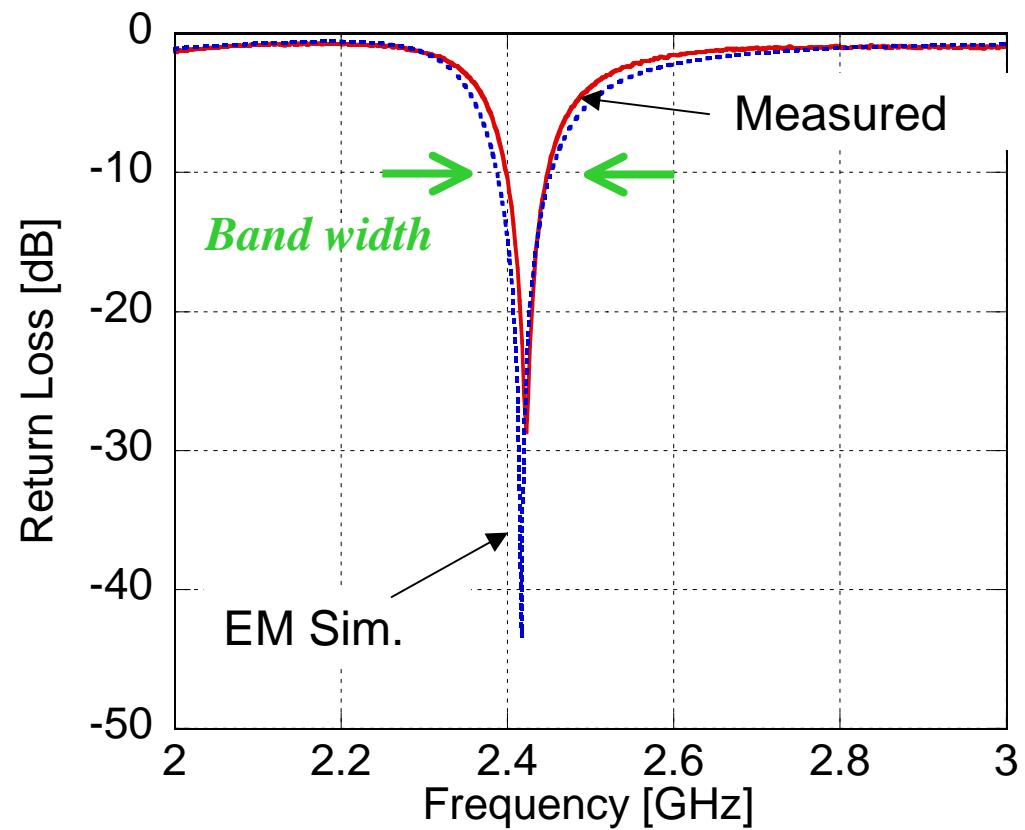
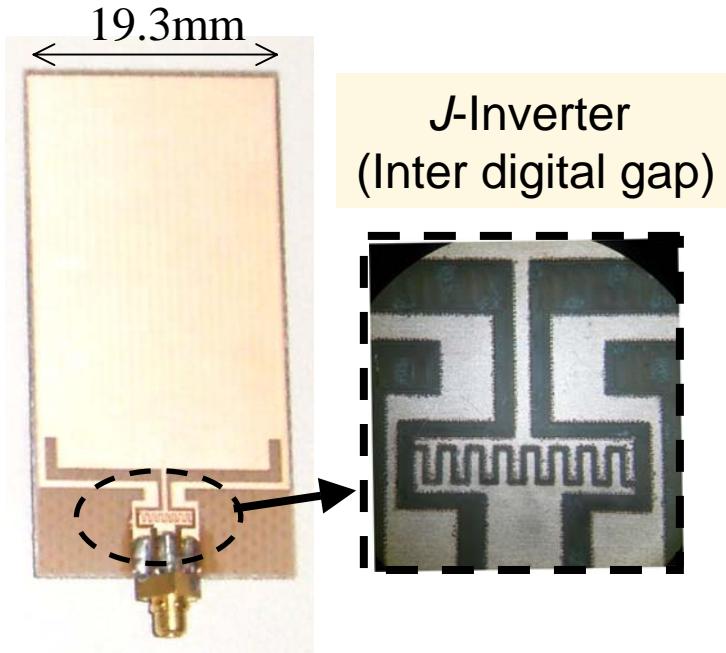


J-inverter

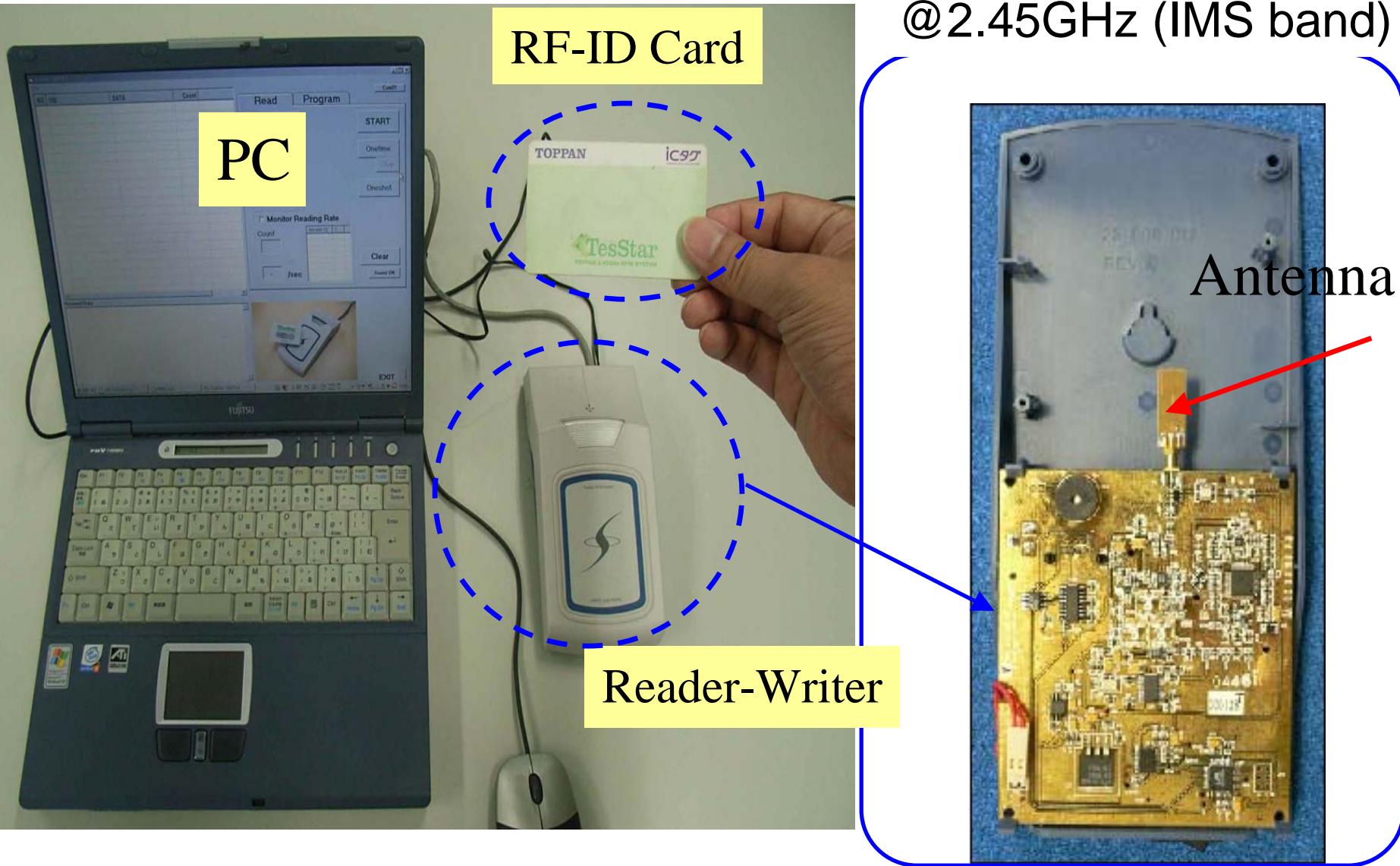


Experimental results of the one-sided directional ESA with CPW matching circuit

Photographs of the antenna



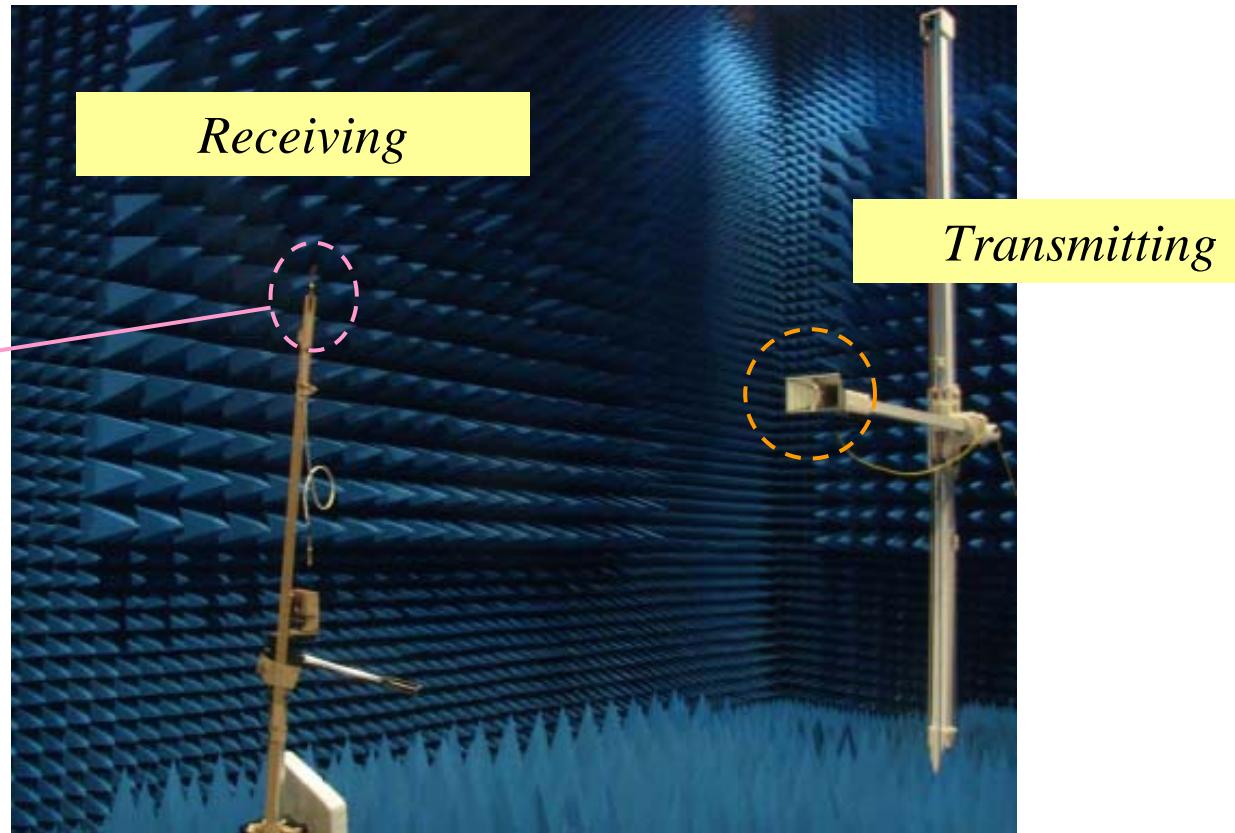
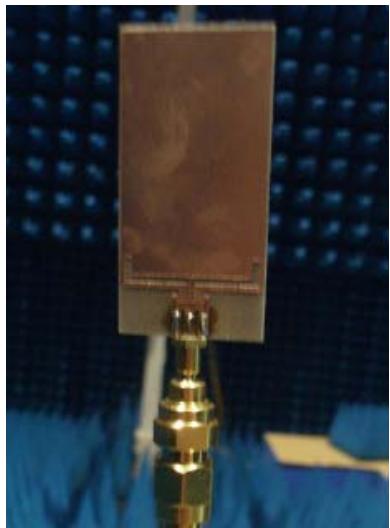
Experimental results of the one-sided directional ESA with CPW matching circuit



Setup of Radiation Pattern Measurement

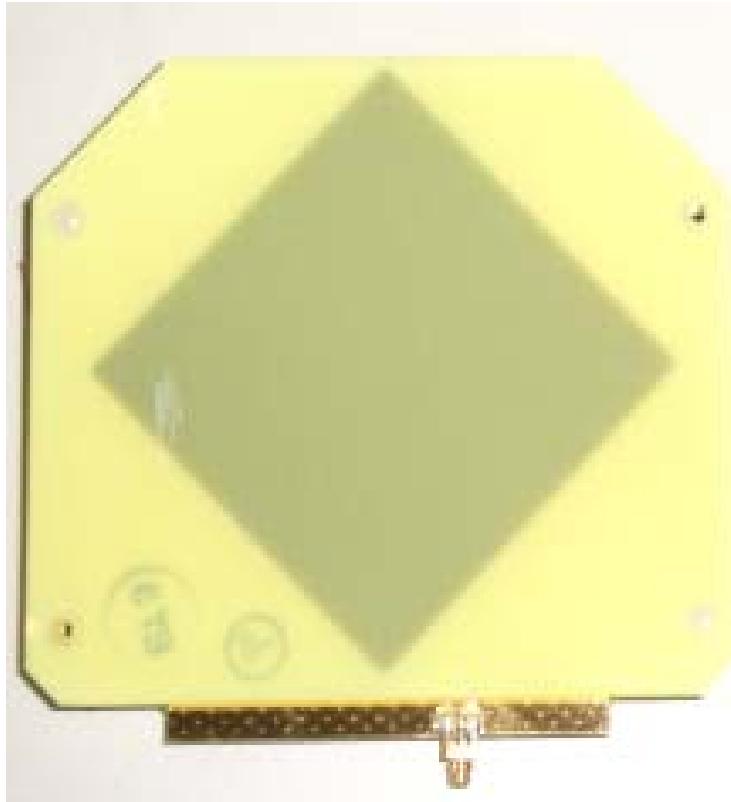
In the anechoic chamber

Test antenna



Turn table

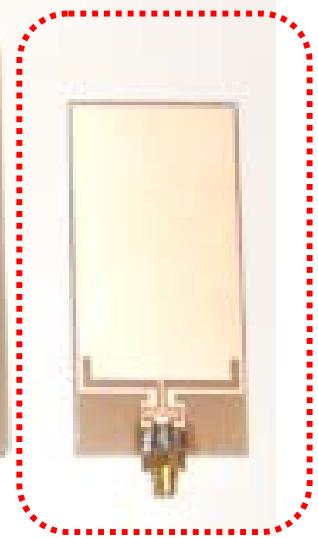
Comparison of the sizes of the one-sided directional antenna



Patch antenna #1
75mm□ × t5mm

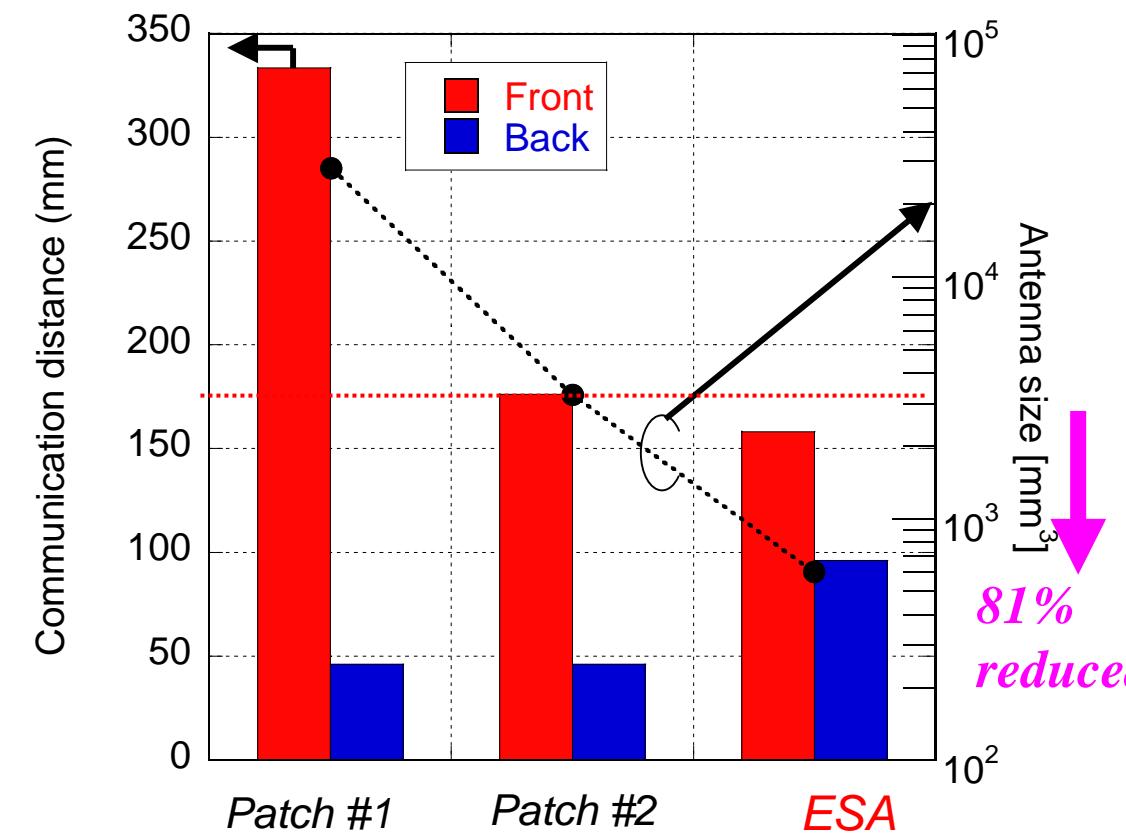


Patch antenna #2
45mm□ × t1.6mm

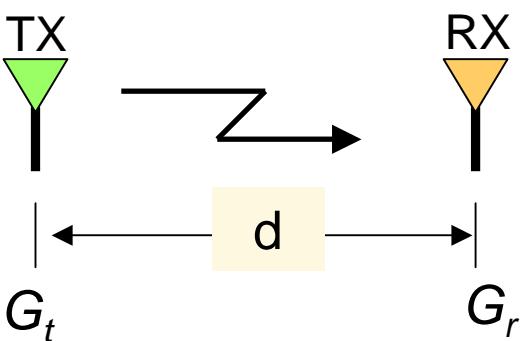


ESA
39 × 19 × t0.8mm

Measured communication distance and antenna size of the patch antenna and ESA



Friis' Transmission Formula

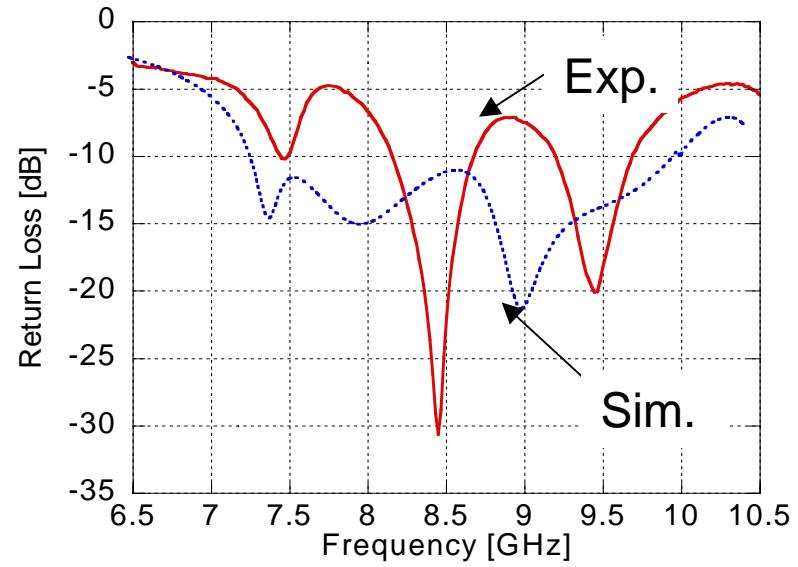
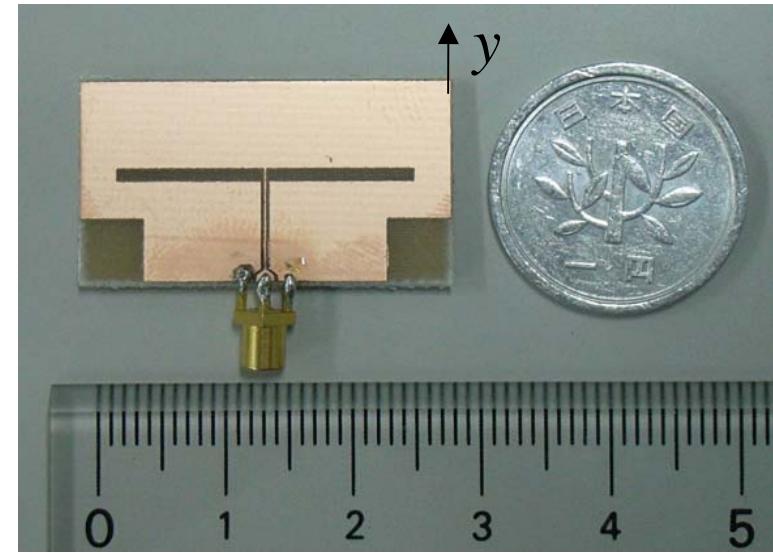


Power received by the RX antenna

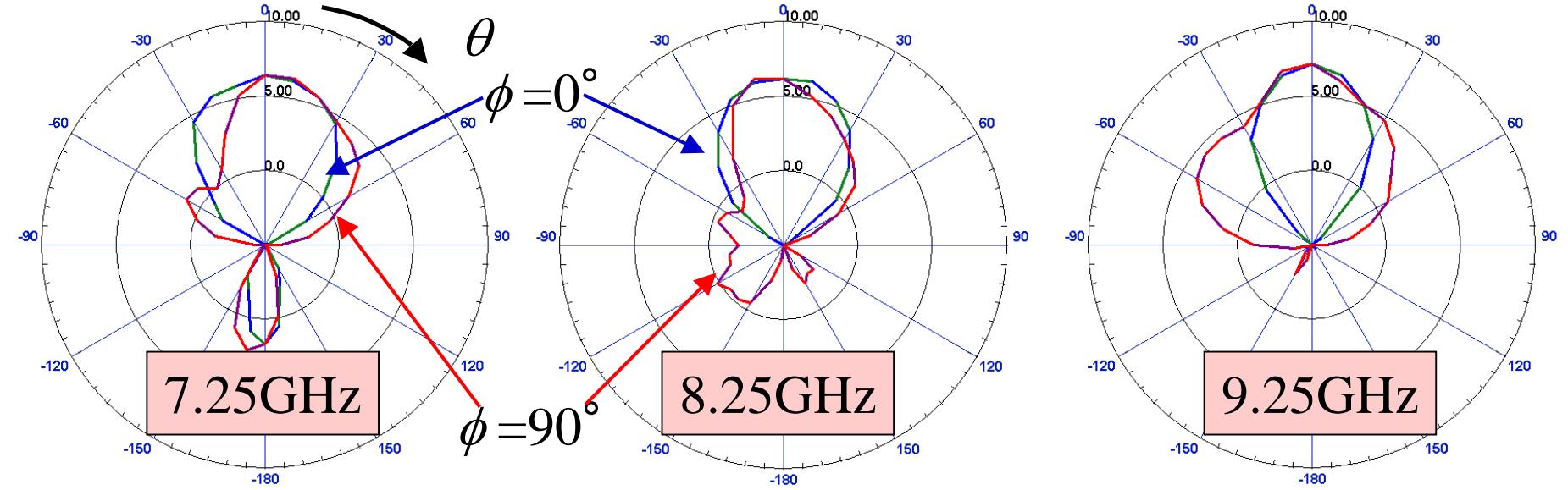
$$W_r = \left(\frac{\lambda}{4\pi d} \right)^2 G_t G_r W_t$$

81%
reduced!

UWB High Band one-sided directional antenna



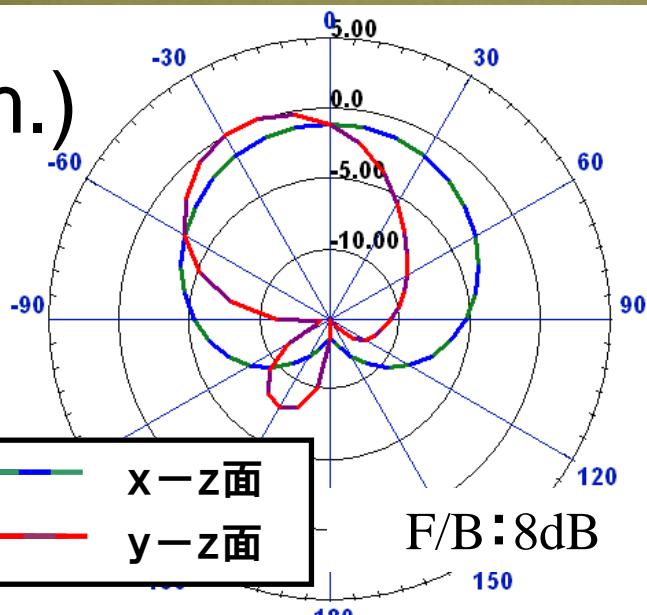
Three resonance—broad band



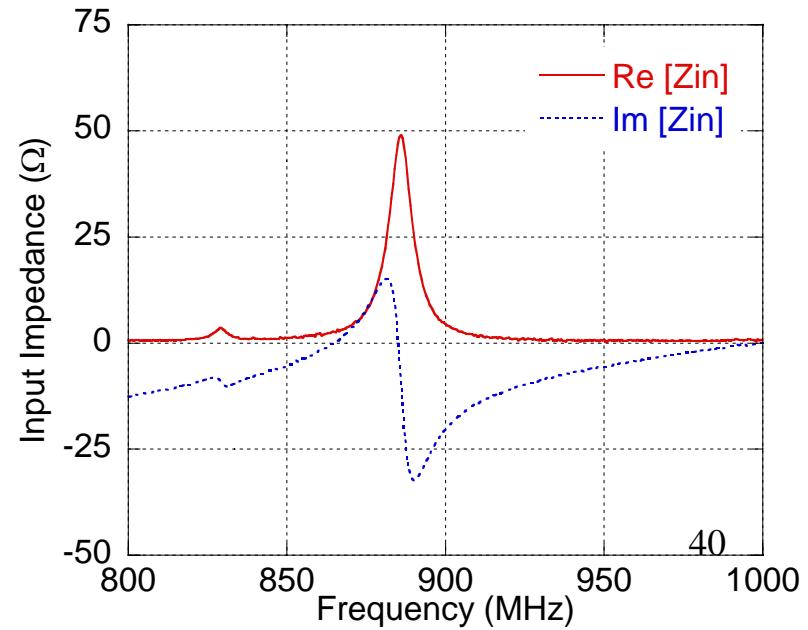
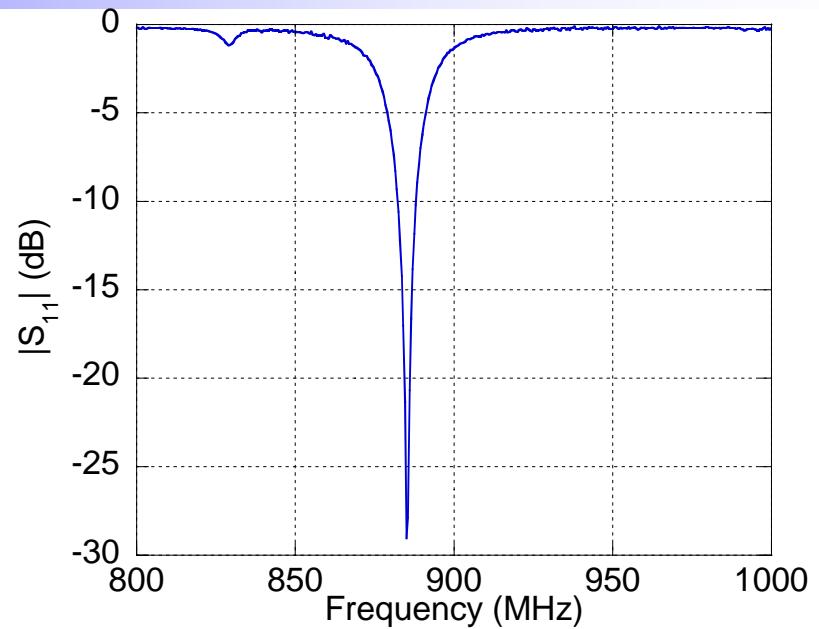
UHF visiting-card size one-sided directional antenna



(Sim.)



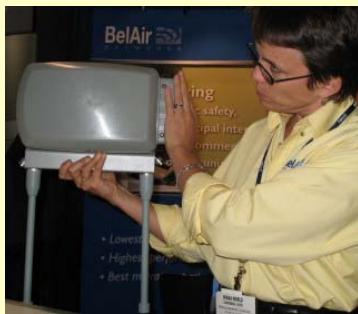
Human body or metal surface like auto mobile.



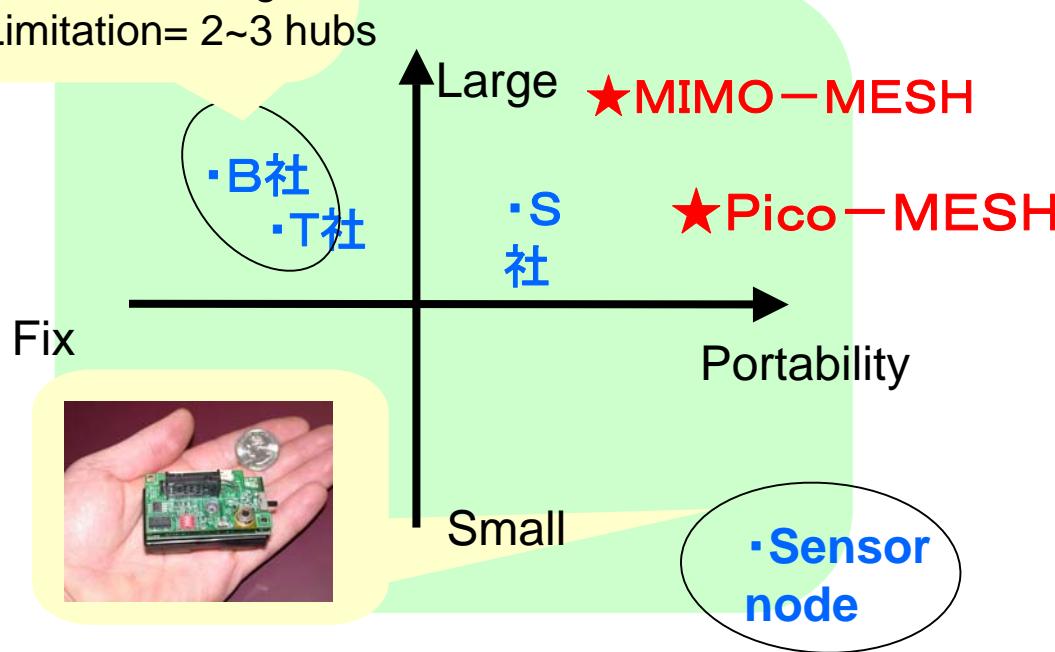
New national project (PICO, MIMO) MESH Network

MIMO-MESH, Pico-MESH

Conventional MESH Device

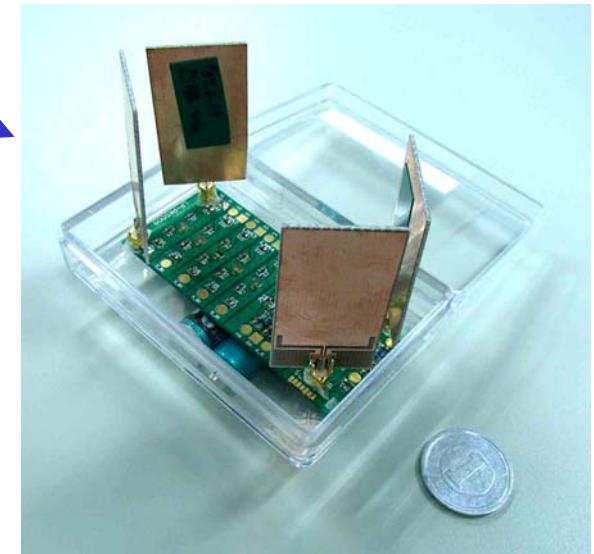


More than 10kg
Limitation= 2~3 hubs



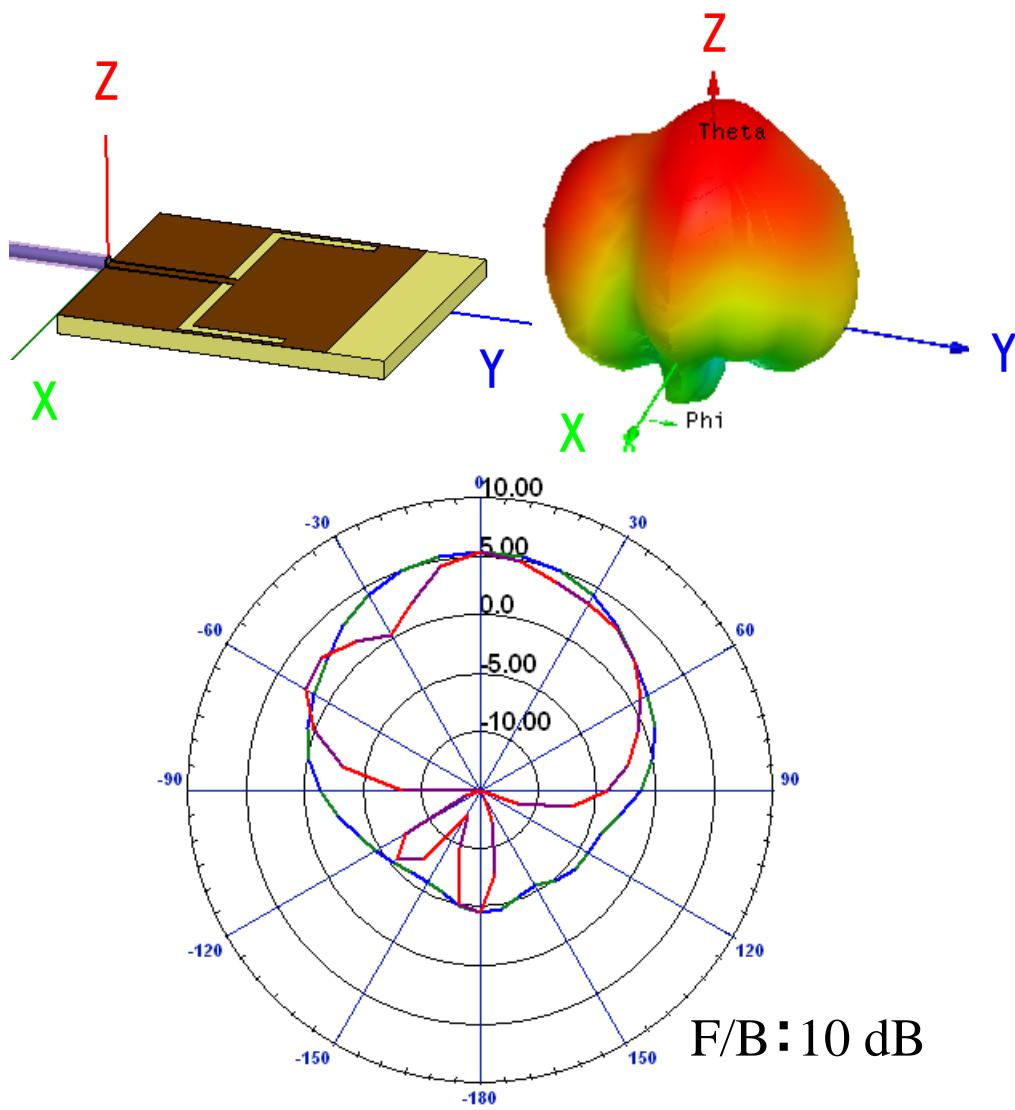
MESH Point

One-sided directional planar antennas



RF front end + IP Core

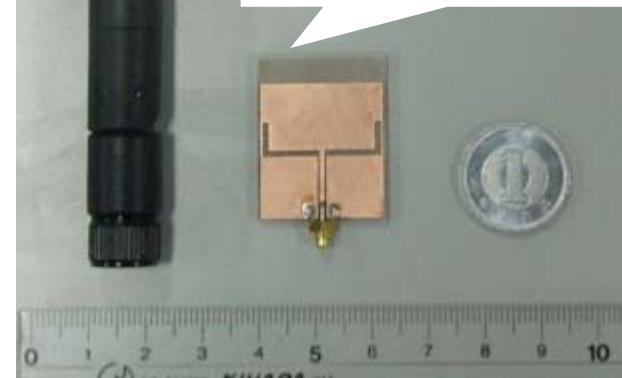
MESH Antenna @5GHz



Conventional
H:15.7mm ×
D:1.1mm
5dBi



New Antenna
22mm × 28mm
5dBi (One-sided
directional)



Measurement system of communication distance

Node

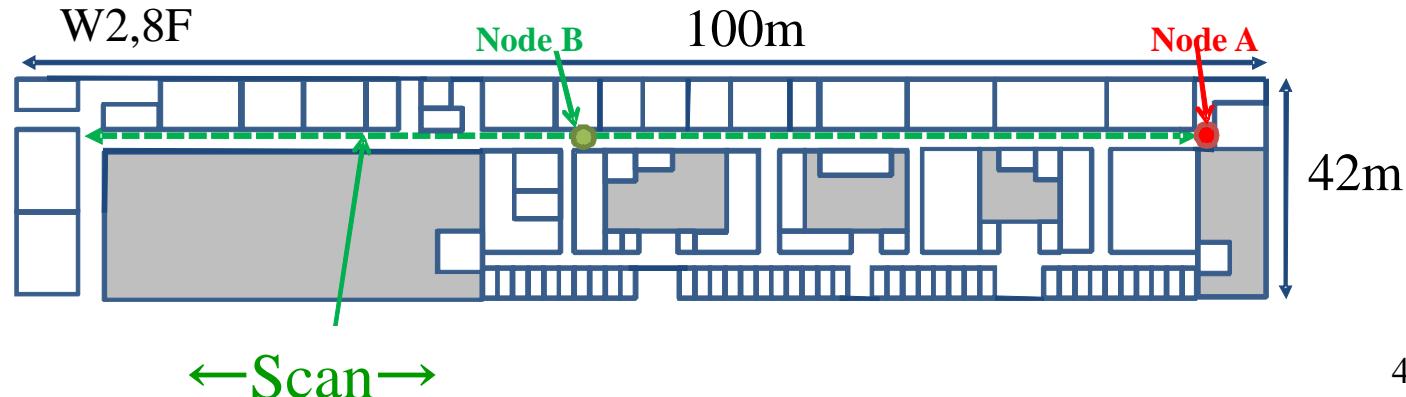


Node Photo

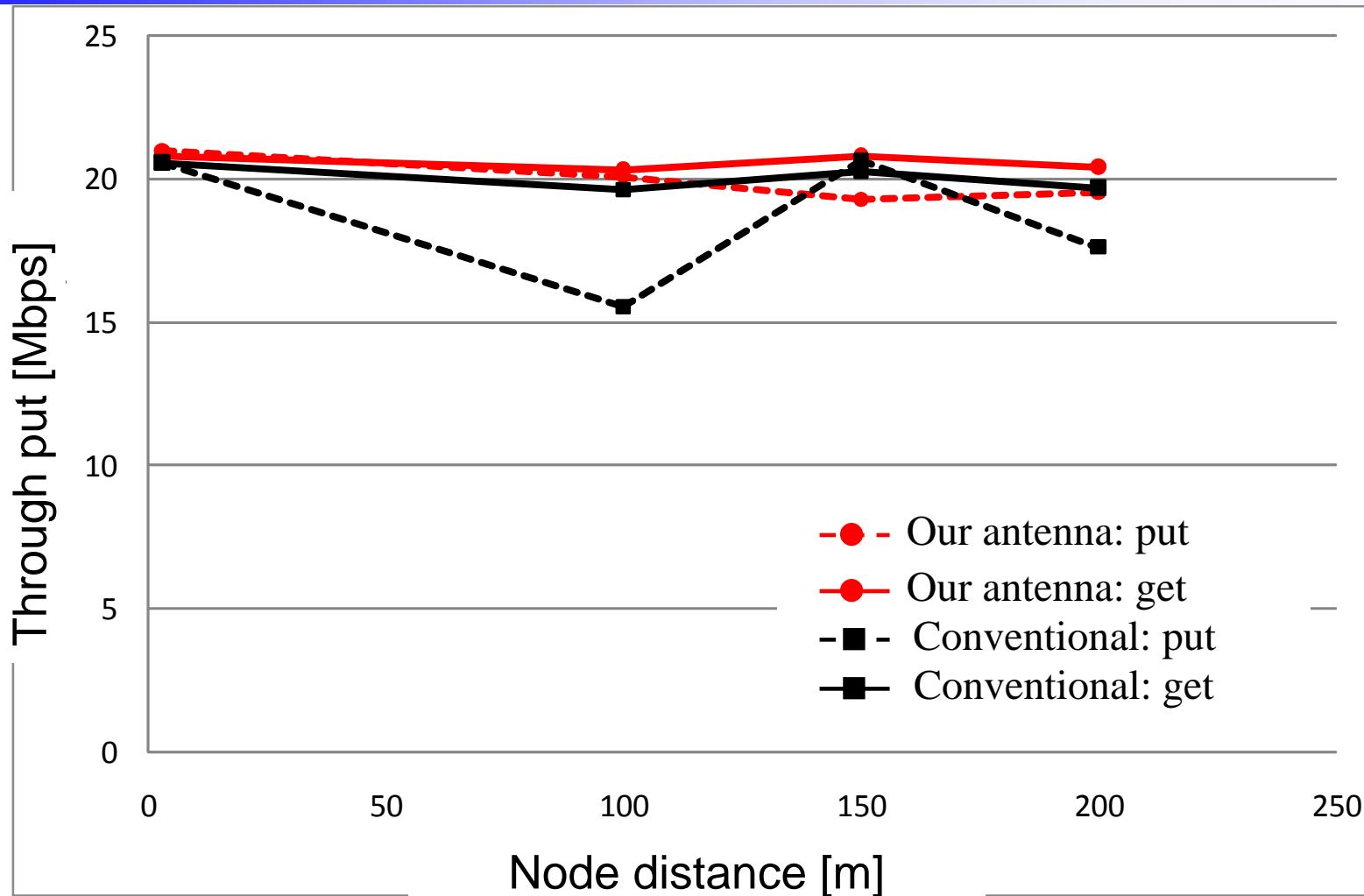


※ Speed: 36Mbps, Frequency: 52ch(5.26GHz), Amp. output: 17dBm(50mW)

Field:
Building

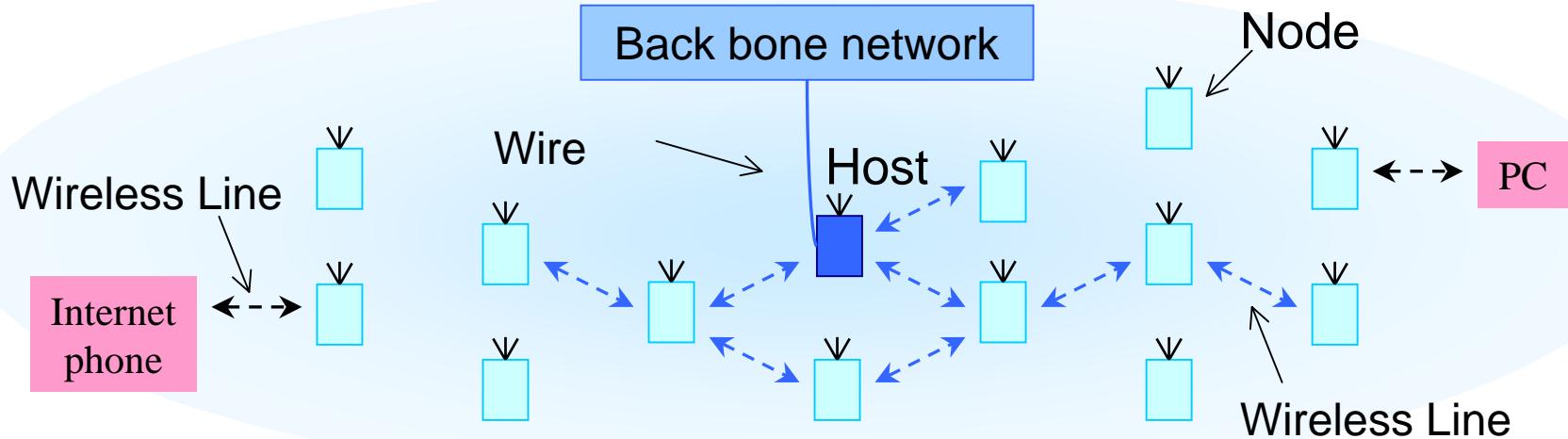


Measured communication distance



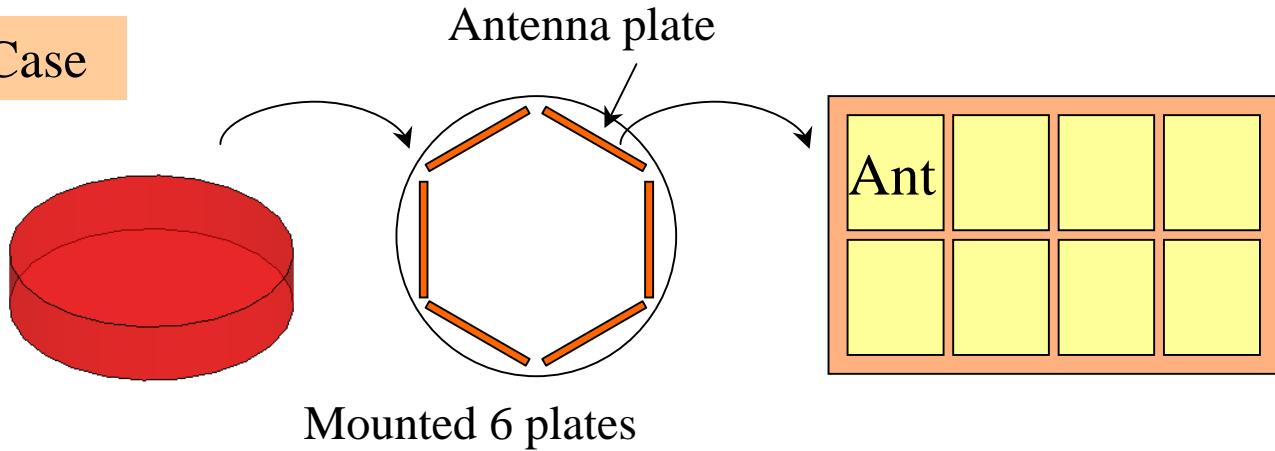
communication distance > 200m

MIMO-MESH Point



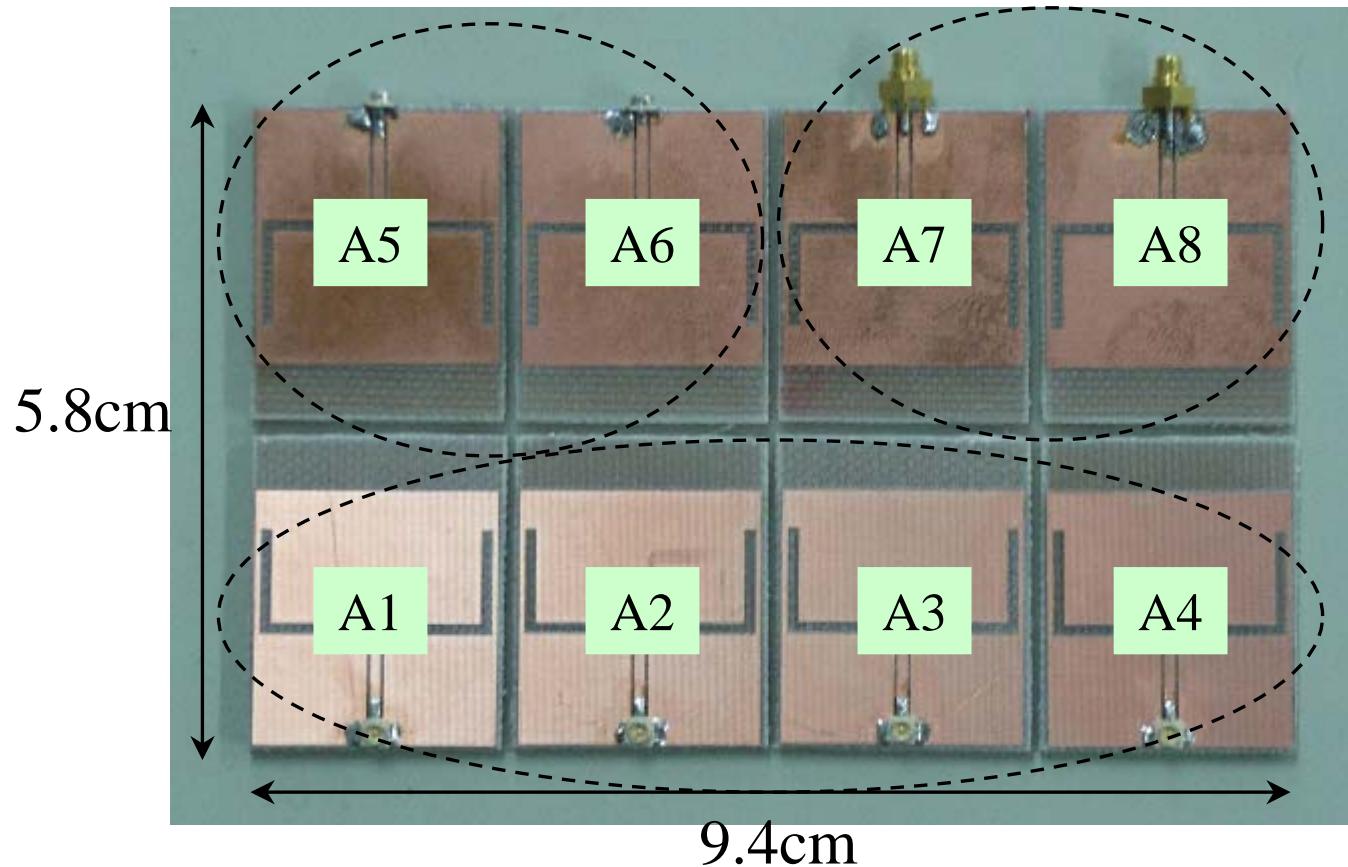
A small antenna is necessary !!

Case



- Small size
- One sided directional
- Wide band
(4.9GHz ~ 5.7GHz)

Antenna plate



Conclusion

- RF COMOS Front-end (RFIC)
- Planer type small antenna

Applications: 3G, .11a,b &g,
MIMO,PICO and UWB

Detail:

RFIC Japan

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